

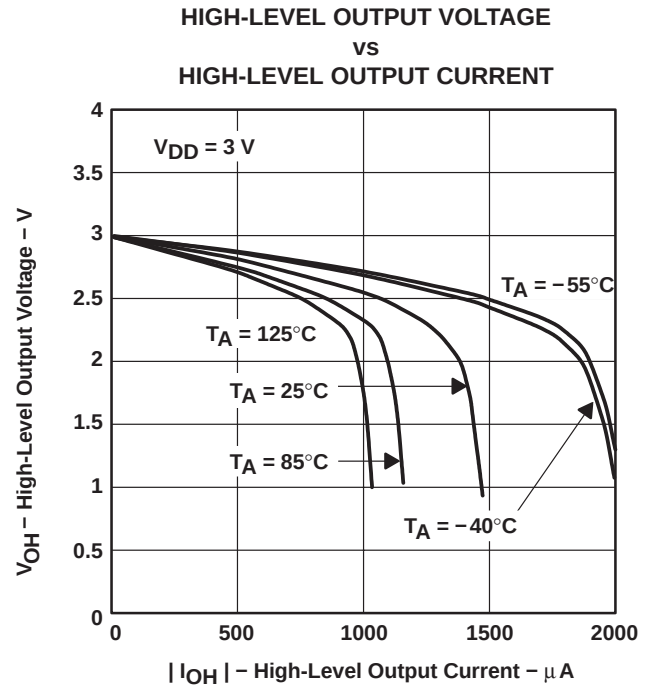
- **Output Swing Includes Both Supply Rails**
- **Low Noise . . . 12 nV/√Hz Typ at f = 1 kHz**
- **Low Input Bias Current . . . 1 pA Typ**
- **Fully Specified for Both Single-Supply and Split-Supply Operation**
- **Low Power . . . 500 μA Max**
- **Common-Mode Input Voltage Range Includes Negative Rail**
- **Low Input Offset Voltage**
950 μV Max at T_A = 25°C (TLV226xA)
- **Wide Supply Voltage Range**
2.7 V to 8 V
- **Macromodel Included**
- **Available in Q-Temp Automotive**
HighRel Automotive Applications
Configuration Control / Print Support
Qualification to Automotive Standards

description

The TLV2262 and TLV2264 are dual and quad low voltage operational amplifiers from Texas Instruments. Both devices exhibit rail-to-rail output performance for increased dynamic range in single or split supply applications. The TLV226x family offers a compromise between the micro-power TLV225x and the ac performance of the TLC227x. It has low supply current for battery-powered applications, while still having adequate ac performance for applications that demand it. This family is fully characterized at 3 V and 5 V and is optimized for low-voltage applications. The noise performance has been dramatically improved over previous generations of CMOS amplifiers. Figure 1 depicts the low level of noise voltage for this CMOS amplifier, which has only 200 μA (typ) of supply current per amplifier.

The TLV226x, exhibiting high input impedance and low noise, are excellent for small-signal conditioning for high-impedance sources, such as piezoelectric transducers. Because of the micro-power dissipation levels combined with 3-V operation, these devices work well in hand-held monitoring and remote-sensing applications. In addition, the rail-to-rail output feature with single or split supplies makes this family a great choice when interfacing with analog-to-digital converters (ADCs). For precision applications, the TLV226xA family is available and has a maximum input offset voltage of 950 μV.

The TLV2262/4 also makes great upgrades to the TLV2332/4 in standard designs. They offer increased output dynamic range, lower noise voltage and lower input offset voltage. This enhanced feature set allows them to be used in a wider range of applications. For applications that require higher output drive and wider input voltage range, see the TLV2432 and TLV2442 devices. If your design requires single amplifiers, please see the TLV2211/21/31 family. These devices are single rail-to-rail operational amplifiers in the SOT-23 package. Their small size and low power consumption make them ideal for high density, battery-powered equipment.



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TLV226x, TLV226xA

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TLV2262 AVAILABLE OPTIONS

T _A	V _{IO} max AT 25°C	PACKAGED DEVICES					
		SMALL OUTLINE (D)	CHIP CARRIER (FK)	CERAMIC DIP (JG)	PLASTIC DIP (P)	TSSOP (PW)	CERAMIC FLATPACK (U)
0°C to 70°C	2.5 mV	TLV2262CD	—	—	TLV2262CP	TLV2262CPWLE	—
–40°C to 125°C	950 µV 2.5 mV	TLV2262AID TLV2262ID	— —	— —	TLV2262AIP TLV2262IP	TLV2262AIPWLE —	— —
–40°C to 125°C	950 µV 2.5 mV	TLV2262AQD TLV2262QD	— —	— —	— —	— —	— —
–55°C to 125°C	950 µV 2.5 mV	— —	TLV2262AMFK TLV2262MFK	TLV2262AMJG TLV2262MJG	— —	— —	TLV2262AMU TLV2262MU

† The D packages are available taped and reeled. Add R suffix to device type (e.g., TLV2262CDR).

‡ The PW package is available only left-end taped and reeled.

§ Chips are tested at 25°C.

¶ For the most current package and ordering information see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.

TLV2264 AVAILABLE OPTIONS

T _A	V _{IO} max AT 25°C	PACKAGED DEVICES					
		SMALL OUTLINE (D)	CHIP CARRIER (FK)	CERAMIC DIP (J)	PLASTIC DIP (N)	TSSOP (PW)	CERAMIC FLATPACK (W)
–40°C to 125°C	950 µV 2.5 mV	TLV2264AID TLV2264ID	— —	— —	TLV2264AIN TLV2264IN	TLV2264AIPWLE —	— —
–40°C to 125°C	950 µV 2.5 mV	TLV2264AQD TLV2264QD	— —	— —	— —	— —	— —
–55°C to 125°C	950 µV 2.5 mV	— —	TLV2264AMFK TLV2264MFK	TLV2264AMJ TLV2264MJ	— —	— —	TLV2264AMW TLV2264MW

† The D packages are available taped and reeled. Add R suffix to device type (e.g., TLV2262IDR).

‡ The PW package is available only left-end taped and reeled.

§ Chips are tested at 25°C.

¶ For the most current package and ordering information see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.

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TLV2262C, TLV2262AC
TLV2262I, TLV2262AI
TLV2262Q, TLV2262AQ
D, P, OR PW PACKAGE
(TOP VIEW)



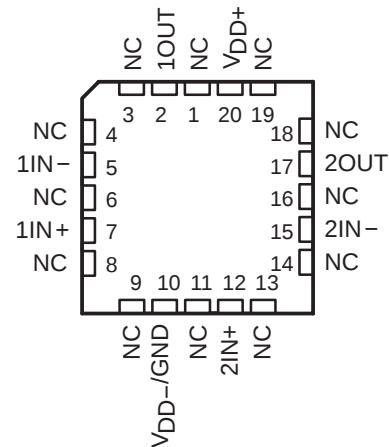
TLV2262M, TLV2262AM
JG PACKAGE
(TOP VIEW)



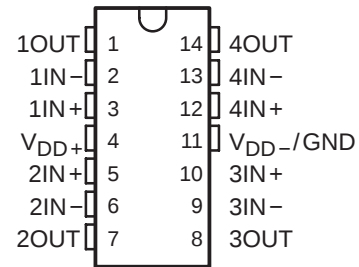
TLV2262M, TLV2262AM
U PACKAGE
(TOP VIEW)



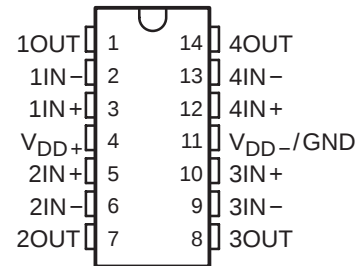
TLV2262M, TLV2262AM
FK PACKAGE
(TOP VIEW)



TLV2264I, TLV2264AI
TLV2264Q, TLV2264AQ
D, N, OR PW PACKAGE
(TOP VIEW)



TLV2264M, TLV2264AM
J OR W PACKAGE
(TOP VIEW)



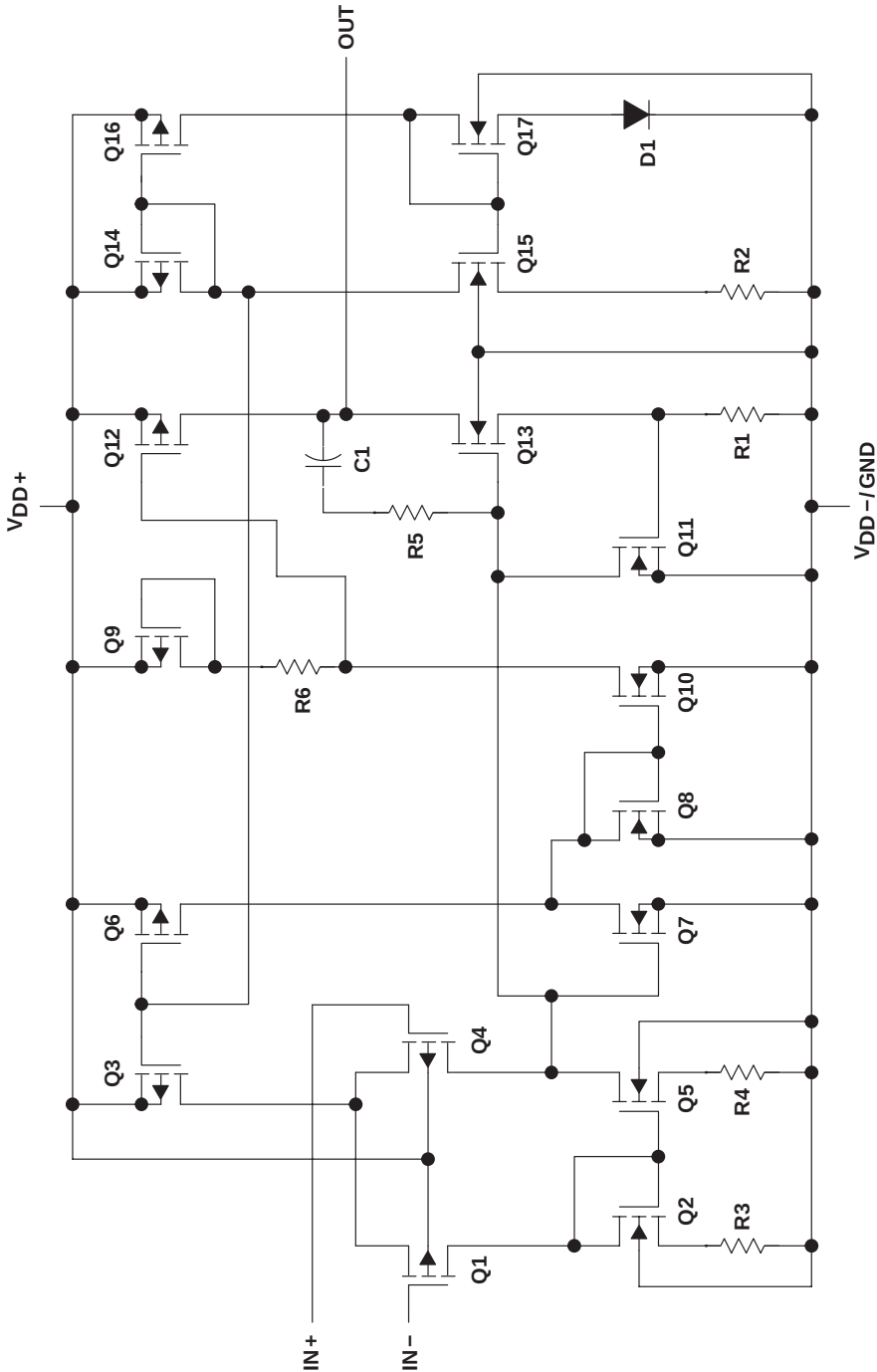
TLV2264M, TLV2264AM
FK PACKAGE
(TOP VIEW)



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equivalent schematic (each amplifier)



ACTUAL DEVICE COMPONENT COUNT†		
COMPONENT	TLV2252	TLV2254
Transistors	38	76
Resistors	28	54
Diodes	9	18
Capacitors	3	6

† Includes both amplifiers and all ESD, bias, and trim circuitry

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

Supply voltage, V_{DD} (see Note 1)	16 V
Differential input voltage, V_{ID} (see Note 2)	$\pm V_{DD}$
Input voltage range, V_I (any input, see Note 1)	$V_{DD} - 0.3 \text{ V}$ to V_{DD+}
Input current, I_I (each input)	$\pm 5 \text{ mA}$
Output current, I_O	$\pm 50 \text{ mA}$
Total current into V_{DD+}	$\pm 50 \text{ mA}$
Total current out of V_{DD-}	$\pm 50 \text{ mA}$
Duration of short-circuit current (at or below) 25°C (see Note 3)	unlimited
Continuous total power dissipation	See Dissipation Rating Table
Operating free-air temperature range, T_A : I suffix	-40°C to 125°C
Q suffix	-40°C to 125°C
M suffix	-55°C to 125°C
Storage temperature range, T_{stg}	-65°C to 150°C

[†] Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values, except differential voltages, are with respect to V_{DD-} .
2. Differential voltages are at the noninverting input with respect to the inverting input. Excessive current flows when input is brought below $V_{DD-} - 0.3 \text{ V}$.
3. The output may be shorted to either supply. Temperature and/or supply voltages must be limited to ensure that the maximum dissipation rating is not exceeded.

DISSIPATION RATING TABLE

PACKAGE	$T_A \leq 25^\circ\text{C}$ POWER RATING	DERATING FACTOR ABOVE $T_A = 25^\circ\text{C}$	$T_A = 85^\circ\text{C}$ POWER RATING	$T_A = 125^\circ\text{C}$ POWER RATING
D-8	725 mW	5.8 mW/°C	377 mW	145 mW
D-14	950 mW	7.6 mW/°C	494 mW	190 mW
FK	1375 mW	11.0 mW/°C	715 mW	275 mW
J	1375 mW	11.0 mW/°C	715 mW	275 mW
JG	1050 mW	8.4 mW/°C	—	210 mW
N	1150 mW	9.2 mW/°C	598 mW	—
P	1000 mW	8.0 mW/°C	520 mW	200 mW
PW-8	525 mW	4.2 mW/°C	273 mW	105 mW
PW-14	700 mW	5.6 mW/°C	364 mW	—
U	700 mW	5.5 mW/°C	—	150 mW
W	700 mW	5.5 mW/°C	370 mW	150 mW

recommended operating conditions

	I SUFFIX		Q SUFFIX		M SUFFIX		UNIT
	MIN	MAX	MIN	MAX	MIN	MAX	
Supply voltage, $V_{DD\pm}$ (see Note 1)	2.7	8	2.7	8	2.7	8	V
Input voltage range, V_I	V_{DD-}	$V_{DD+} - 1.3$	V_{DD-}	$V_{DD+} - 1.3$	V_{DD-}	$V_{DD+} - 1.3$	V
Common-mode input voltage, V_{IC}	V_{DD-}	$V_{DD+} - 1.3$	V_{DD-}	$V_{DD+} - 1.3$	V_{DD-}	$V_{DD+} - 1.3$	V
Operating free-air temperature, T_A	-40	125	-40	125	-55	125	°C

NOTE 1: All voltage values, except differential voltages, are with respect to V_{DD-} .

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TLV2262I electrical characteristics at specified free-air temperature, $V_{DD} = 3\text{ V}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	$T_A^\dagger$	TLV2262I			TLV2262AI			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{IO} Input offset voltage	$V_{DD\pm} = \pm 1.5\text{ V}$, $V_{IC} = 0$, $V_O = 0$, $R_S = 50\ \Omega$	25°C		300	2500		300	950	μV
		Full range			3000			1500	
α_{VIO} Temperature coefficient of input offset voltage		25°C to 85°C		2			2		$\mu\text{V}/^\circ\text{C}$
Input offset voltage long-term drift (see Note 4)		25°C		0.003			0.003		$\mu\text{V}/\text{mo}$
I_{IO} Input offset current		25°C		0.5	60		0.5	60	pA
		85°C			150			150	
		Full range			800			800	
I_{IB} Input bias current		25°C		1	60		1	60	pA
		85°C			150			150	
		Full range			800			800	
V_{ICR} Common-mode input voltage range	$R_S = 50\ \Omega$, $ V_{IO} \leq 5\text{ mV}$	25°C	0 to 2	-0.3 to 2.2		0 to 2	-0.3 to 2.2		V
		Full range	0 to 1.7			0 to 1.7			
V_{OH} High-level output voltage	$I_{OH} = -20\ \mu\text{A}$	25°C		2.99			2.99		V
	$I_{OH} = -100\ \mu\text{A}$	25°C		2.85			2.85		
		Full range		2.825			2.825		
	$I_{OH} = -400\ \mu\text{A}$	25°C		2.7			2.7		
V_{OL} Low-level output voltage	$V_{IC} = 1.5\text{ V}$, $I_{OL} = 50\ \mu\text{A}$	25°C		10			10		mV
	$V_{IC} = 1.5\text{ V}$, $I_{OL} = 500\ \mu\text{A}$	25°C		100			100		
		Full range			150			150	
	$V_{IC} = 1.5\text{ V}$, $I_{OL} = 1\text{ mA}$	25°C		200			200		
A_{VD} Large-signal differential voltage amplification	$V_{IC} = 1.5\text{ V}$, $V_O = 1\text{ V to } 2\text{ V}$	$R_L = 50\text{ k}\Omega^\ddagger$	25°C	60	100		60	100	V/mV
			Full range	30			30		
		$R_L = 1\text{ M}\Omega^\ddagger$	25°C		100			100	
$r_{i(d)}$ Differential input resistance		25°C		10^{12}			10^{12}		Ω
$r_{i(c)}$ Common-mode input resistance		25°C		10^{12}			10^{12}		Ω
$C_{i(c)}$ Common-mode input capacitance	$f = 10\text{ kHz}$, P package	25°C		8			8		pF
z_o Closed-loop output impedance	$f = 100\text{ kHz}$, $A_V = 10$	25°C		270			270		Ω
CMRR Common-mode rejection ratio	$V_{IC} = 0\text{ to } 1.7\text{ V}$, $V_O = 1.5\text{ V}$, $R_S = 50\ \Omega$	25°C		65	75		65	77	dB
		Full range		60			60		
k_{SVR} Supply voltage rejection ratio ($\Delta V_{DD}/\Delta V_{IO}$)	$V_{DD} = 2.7\text{ V to } 8\text{ V}$, $V_{IC} = V_{DD}/2$, No load	25°C		80	95		80	100	dB
		Full range		80			80		

† Full range is -40°C to 125°C.

‡ Referenced to 1.5 V

NOTE 4: Typical values are based on the input offset voltage shift observed through 500 hours of operating life test at $T_A = 150^\circ\text{C}$ extrapolated to $T_A = 25^\circ\text{C}$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.



TLV2262I electrical characteristics at specified free-air temperature, $V_{DD} = 3\text{ V}$ (unless otherwise noted) (continued)

PARAMETER	TEST CONDITIONS	$T_A^\dagger$	TLV2262I			TLV2262AI			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
I_{DD} Supply current	$V_O = 1.5\text{ V}$, No load	25°C		400	500		400	500	μA
		Full range			500			500	

† Full range is – 40°C to 125°C.

TLV2262I operating characteristics at specified free-air temperature, $V_{DD} = 3\text{ V}$

PARAMETER	TEST CONDITIONS		$T_A^\dagger$	TLV2262I			TLV2262AI			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	
SR Slew rate at unity gain	$V_O = 1.1\text{ V to }1.9\text{ V}$, $R_L = 50\text{ k}\Omega^\ddagger$, $C_L = 100\text{ pF}^\ddagger$		25°C	0.35	0.55		0.35	0.55		$\text{V}/\mu\text{s}$
			Full range	0.3			0.3			
V_n Equivalent input noise voltage	$f = 10\text{ Hz}$		25°C		43			43		$\text{nV}/\sqrt{\text{Hz}}$
	$f = 1\text{ kHz}$		25°C		12			12		
$V_{N(PP)}$ Peak-to-peak equivalent input noise voltage	$f = 0.1\text{ Hz to }1\text{ Hz}$		25°C		0.6			0.6		μV
	$f = 0.1\text{ Hz to }10\text{ Hz}$		25°C		1			1		
I_n Equivalent input noise current			25°C		0.6			0.6		$\text{fA}/\sqrt{\text{Hz}}$
THD + N Total harmonic distortion plus noise	$V_O = 0.5\text{ V to }2.5\text{ V}$, $f = 20\text{ kHz}$, $R_L = 50\text{ k}\Omega^\ddagger$	$A_V = 1$	25°C		0.03%			0.03%		
		$A_V = 10$			0.05%			0.05%		
Gain-bandwidth product	$f = 1\text{ kHz}$, $R_L = 50\text{ k}\Omega^\ddagger$, $C_L = 100\text{ pF}^\ddagger$		25°C		0.67			0.67		MHz
B_{OM} Maximum output-swing bandwidth	$V_{O(PP)} = 1\text{ V}$, $R_L = 50\text{ k}\Omega^\ddagger$, $C_L = 100\text{ pF}^\ddagger$	$A_V = 1$	25°C		395			395		kHz
t_s Settling time	$A_V = -1$, Step = 1 V to 2 V, $R_L = 50\text{ k}\Omega^\ddagger$, $C_L = 100\text{ pF}^\ddagger$	$T_o = 0.1\%$	25°C		5.6			5.6		μs
		$T_o = 0.01\%$			12.5			12.5		
ϕ_m Phase margin at unity gain	$R_L = 50\text{ k}\Omega^\ddagger$, $C_L = 100\text{ pF}^\ddagger$		25°C		55°			55°		
Gain margin			25°C		11			11		dB

† Full range is – 40°C to 125°C.

‡ Referenced to 1.5 V

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TLV2262I electrical characteristics at specified free-air temperature, $V_{DD} = 5\text{ V}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	$T_A^\dagger$	TLV2262I			TLV2262AI			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{IO} Input offset voltage	$V_{DD} = \pm 2.5\text{ V}, V_{IC} = 0, V_O = 0, R_S = 50\ \Omega$	25°C	300	2500		300	950		μV
		Full range		3000			1500		
α_{VIO} Temperature coefficient of input offset voltage		25°C to 85°C	2			2			$\mu\text{V}/^\circ\text{C}$
Input offset voltage long-term drift (see Note 4)		25°C	0.003			0.003			$\mu\text{V}/\text{mo}$
I_{IO} Input offset current		25°C	0.5	60		0.5	60		pA
		85°C		150			150		
		Full range		800			800		
I_{IB} Input bias current		25°C	1	60		1	60		pA
		85°C		150			150		
		Full range		800			800		
V_{ICR} Common-mode input voltage range	$ V_{IO} \leq 5\text{ mV}, R_S = 50\ \Omega$	25°C	0 to 4	-0.3 to 4.2		0 to 4	-0.3 to 4.2		V
		Full range	0 to 3.5			0 to 3.5			
V_{OH} High-level output voltage	$I_{OH} = -20\ \mu\text{A}$	25°C	4.99			4.99			V
	$I_{OH} = -100\ \mu\text{A}$	25°C	4.85	4.94		4.85	4.94		
		Full range	4.82			4.82			
	$I_{OH} = -400\ \mu\text{A}$	25°C	4.7	4.85		4.7	4.85		
		Full range	4.6			4.6			
V_{OL} Low-level output voltage	$V_{IC} = 2.5\text{ V}, I_{OL} = 50\ \mu\text{A}$	25°C	0.01			0.01			V
		25°C	0.09	0.15		0.09	0.15		
	$V_{IC} = 2.5\text{ V}, I_{OL} = 500\ \mu\text{A}$	Full range		0.15			0.15		
		25°C	0.2	0.3		0.2	0.3		
	$V_{IC} = 2.5\text{ V}, I_{OL} = 1\text{ mA}$	Full range		0.3			0.3		
A_{VD} Large-signal differential voltage amplification	$V_{IC} = 2.5\text{ V}, V_O = 1\text{ V to } 4\text{ V}$	25°C	80	170		80	170		V/mV
		Full range	55			55			
		25°C	550			550			
$r_{i(d)}$ Differential input resistance		25°C	10^{12}			10^{12}			Ω
$r_{i(c)}$ Common-mode input resistance		25°C	10^{12}			10^{12}			Ω
$C_{i(c)}$ Common-mode input capacitance	$f = 10\text{ kHz}, \text{ P package}$	25°C	8			8			pF
z_o Closed-loop output impedance	$f = 100\text{ kHz}, A_V = 10$	25°C	240			240			Ω
CMRR Common-mode rejection ratio	$V_{IC} = 0\text{ to } 2.7\text{ V}, V_O = 2.5\text{ V}, R_S = 50\ \Omega$	25°C	70	83		70	83		dB
		Full range	70			70			
k_{SVR} Supply voltage rejection ratio ($\Delta V_{DD}/\Delta V_{IO}$)	$V_{DD} = 4.4\text{ V to } 8\text{ V}, V_{IC} = V_{DD}/2, \text{ No load}$	25°C	80	95		80	95		dB
		Full range	80			80			

† Full range is -40°C to 125°C.

‡ Referenced to 2.5 V

NOTE 4: Typical values are based on the input offset voltage shift observed through 500 hours of operating life test at $T_A = 150^\circ\text{C}$ extrapolated to $T_A = 25^\circ\text{C}$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.



TLV2262I electrical characteristics at specified free-air temperature, $V_{DD} = 5\text{ V}$ (unless otherwise noted) (continued)

PARAMETER	TEST CONDITIONS	$T_A^\dagger$	TLV2262I			TLV2262AI			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
I_{DD} Supply current	$V_O = 2.5\text{ V}$, No load	25°C		400	500		400	500	μA
		Full range			500			500	

† Full range is -40°C to 125°C .

TLV2262I operating characteristics at specified free-air temperature, $V_{DD} = 5\text{ V}$

PARAMETER		TEST CONDITIONS		T _A [†]	TLV2262I			TLV2262AI			UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	
SR	Slew rate at unity gain	V _O = 1.5 V to 3.5 V, R _L = 50 kΩ [‡] , C _L = 100 pF [‡]		25°C	0.35	0.55		0.35	0.55		V/μs
				Full range	0.3			0.3			
V _n	Equivalent input noise voltage	f = 10 Hz		25°C	40			40			nV/√Hz
		f = 1 kHz		25°C	12			12			
V _{N(PP)}	Peak-to-peak equivalent input noise voltage	f = 0.1 Hz to 1 Hz		25°C	0.7			0.7			μV
		f = 0.1 Hz to 10 Hz		25°C	1.3			1.3			
I _n	Equivalent input noise current			25°C	0.6			0.6			fA/√Hz
THD + N	Total harmonic distortion plus noise	V _O = 0.5 V to 2.5 V, f = 20 kHz, R _L = 50 kΩ [‡]	A _V = 1	25°C	0.017%			0.017%			
			A _V = 10		0.03%			0.03%			
	Gain-bandwidth product	f = 50 kHz, R _L = 50 kΩ [‡] , C _L = 100 pF [‡]		25°C	0.71			0.71			MHz
B _{OM}	Maximum output-swing bandwidth	V _{O(PP)} = 2 V, R _L = 50 kΩ [‡] ,	A _V = 1, C _L = 100 pF [‡]	25°C	185			185			kHz
t _s	Settling time	A _V = −1, Step = 0.5 V to 2.5 V, R _L = 50 kΩ [‡] , C _L = 100 pF [‡]	To 0.1%	25°C	6.4			6.4			μs
			To 0.01%		14.1			14.1			
φ _m	Phase margin at unity gain	R _L = 50 kΩ [‡] , C _L = 100 pF [‡]		25°C	56°			56°			
	Gain margin			25°C	11			11			dB

† Full range is -40°C to 125°C .

‡ Referenced to 2.5 V

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TLV2264I electrical characteristics at specified free-air temperature, $V_{DD} = 3\text{ V}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS		T _A †	TLV2264I			TLV2264AI			UNIT	
					MIN	TYP	MAX	MIN	TYP	MAX		
V _{IO}	Input offset voltage	V _{DD±} = ±1.5 V, V _{IC} = 0, V _O = 0, R _S = 50 Ω		25°C	300	2500		300	950	μV		
	Full range			3000			1500					
αV _{IO}	Temperature coefficient of input offset voltage			25°C to 85°C	2			2			μV/°C	
	Input offset voltage long-term drift (see Note 4)			25°C	0.003			0.003			μV/mo	
I _{IO}	Input offset current			25°C	0.5			60	0.5			pA
				85°C				150	150			
				Full range				800	800			
I _{IB}	Input bias current			25°C	1			60	1			pA
				85°C				150	150			
				Full range				800	800			
V _{ICR}	Common-mode input voltage range	R _S = 50 Ω, V _{IO} ≤ 5 mV	25°C	0 to 2	−0.3 to 2.2			0 to 2	−0.3 to 2.2		V	
			Full range	0 to 1.7			0 to 1.7					
V _{OH}	High-level output voltage	I _{OH} = −20 μA	25°C	2.99			2.99			V		
		I _{OH} = −100 μA	25°C	2.85			2.85					
			Full range	2.825			2.825					
		I _{OH} = −400 μA	25°C	2.7			2.7					
			Full range	2.65			2.65					
V _{OL}	Low-level output voltage	V _{IC} = 1.5 V, I _{OL} = 50 μA	25°C	10			10			mV		
			25°C	100			100					
		V _{IC} = 1.5 V, I _{OL} = 500 μA	Full range	150			150					
			V _{IC} = 1.5 V, I _{OL} = 1 mA	25°C	200			200				
		Full range		300			300					
A _{VD}	Large-signal differential voltage amplification	V _{IC} = 1.5 V, V _O = 1 to 2 V	R _L = 50 kΩ‡	25°C	60	100		60	100	V/mV		
				Full range	30			30				
			R _L = 1 MΩ‡	25°C	100			100				
r _{i(d)}	Differential input resistance			25°C	10 ¹²			10 ¹²			Ω	
r _{i(c)}	Common-mode input resistance			25°C	10 ¹²			10 ¹²			Ω	
c _{i(c)}	Common-mode input capacitance	f = 10 kHz,	N package	25°C	8			8			pF	
z _o	Closed-loop output impedance	f = 100 kHz,	A _V = 10	25°C	270			270			Ω	
CMRR	Common-mode rejection ratio	V _{IC} = 0 to 1.7 V, V _O = 1.5 V, R _S = 50 Ω	25°C	65	75		65	77	dB			
			Full range	60			60					
k _{SVR}	Supply voltage rejection ratio (ΔV _{DD} /ΔV _{IO})	V _{DD} = 2.7 V to 8 V, V _{IC} = V _{DD} /2, No load	25°C	80	95		80	100	dB			
			Full range	80			80					

† Full range is -40°C to 125°C .

‡ Referenced to 1.5 V

NOTE 4: Typical values are based on the input offset voltage shift observed through 500 hours of operating life test at $T_A = 150^\circ\text{C}$ extrapolated to $T_A = 25^\circ\text{C}$ using the Arrhenius equation and assuming an activation energy of 0.96 eV .



TLV2264I electrical characteristics at specified free-air temperature, $V_{DD} = 3\text{ V}$ (unless otherwise noted) (continued)

PARAMETER	TEST CONDITIONS	$T_A^\dagger$	TLV2264I			TLV2264AI			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
I_{DD} Supply current (four amplifiers)	$V_O = 1.5\text{ V}$, No load	25°C		0.8	1		0.8	1	mA
		Full range			1			1	

† Full range is – 40°C to 125°C.

TLV2264I operating characteristics at specified free-air temperature, $V_{DD} = 3\text{ V}$

PARAMETER		TEST CONDITIONS		T _A [†]	TLV2264I			TLV2264AI			UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	
SR	Slew rate at unity gain	V _O = 0.7 V to 1.7 V, R _L = 50 kΩ [‡] , C _L = 100 pF [‡]		25°C	0.35	0.55		0.35	0.55		V/μs
				Full range	0.3			0.3			
V _n	Equivalent input noise voltage	f = 10 Hz		25°C	43			43			nV/√Hz
		f = 1 kHz		25°C	12			12			
V _{N(PP)}	Peak-to-peak equivalent input noise voltage	f = 0.1 Hz to 1 Hz		25°C	0.6			0.6			μV
		f = 0.1 Hz to 10 Hz		25°C	1			1			
I _n	Equivalent input noise current			25°C	0.6			0.6			fA/√Hz
THD + N	Total harmonic distortion plus noise	V _O = 0.5 V to 2.5 V, f = 20 kHz, R _L = 50 kΩ [‡]	A _V = 1	25°C	0.03%			0.03%			
			A _V = 10		0.05%			0.05%			
	Gain-bandwidth product	f = 1 kHz, R _L = 50 kΩ [‡] , C _L = 100 pF [‡]		25°C	0.67			0.67			MHz
B _{OM}	Maximum output-swing bandwidth	V _{O(PP)} = 1 V, R _L = 50 kΩ [‡] , C _L = 100 pF [‡]		25°C	395			395			kHz
t _s	Settling time	A _V = −1, Step = 1 V to 2 V, R _L = 50 kΩ [‡] , C _L = 100 pF [‡]	To 0.1%	25°C	5.6			5.6			μs
			To 0.01%		12.5			12.5			
φ _m	Phase margin at unity gain	R _L = 50 kΩ [‡] , C _L = 100 pF [‡]		25°C	55°			55°			
	Gain margin			25°C	11			11			dB

† Full range is – 40°C to 125°C.

‡ Referenced to 1.5 V

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TLV2264I electrical characteristics at specified free-air temperature, $V_{DD} = 5\text{ V}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	$T_A^\dagger$	TLV2264I			TLV2264AI			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{IO} Input offset voltage	$V_{DD} = \pm 2.5\text{ V}$, $V_{IC} = 0$, $V_O = 0$, $R_S = 50\ \Omega$	25°C	300	2500		300	950		μV
		Full range		3000			1500		
α_{VIO} Temperature coefficient of input offset voltage		25°C to 85°C	2			2			$\mu\text{V}/^\circ\text{C}$
Input offset voltage long-term drift (see Note 4)		25°C	0.003			0.003			$\mu\text{V}/\text{mo}$
I_{IO} Input offset current		25°C	0.5	60		0.5	60		pA
		85°C		150			150		
		Full range		800			800		
I_{IB} Input bias current		25°C	1	60		1	60		pA
		85°C		150			150		
		Full range		800			800		
V_{ICR} Common-mode input voltage range	$ V_{IO} \leq 5\text{ mV}$, $R_S = 50\ \Omega$	25°C	0 to 4	-0.3 to 4.2		0 to 4	-0.3 to 4.2		V
		Full range	0 to 3.5			0 to 3.5			
V_{OH} High-level output voltage	$I_{OH} = -20\ \mu\text{A}$	25°C		4.99			4.99		V
	$I_{OH} = -100\ \mu\text{A}$	25°C	4.85	4.94		4.85	4.94		
		Full range	4.82			4.82			
	$I_{OH} = -400\ \mu\text{A}$	25°C	4.7	4.85		4.7	4.85		
		Full range	4.6			4.6			
V_{OL} Low-level output voltage	$V_{IC} = 2.5\text{ V}$, $I_{OL} = 50\ \mu\text{A}$	25°C		0.01			0.01		V
	$V_{IC} = 2.5\text{ V}$, $I_{OL} = 500\ \mu\text{A}$	25°C		0.09	0.15		0.09	0.15	
		Full range			0.15			0.15	
	$V_{IC} = 2.5\text{ V}$, $I_{OL} = 1\text{ mA}$	25°C		0.2	0.3		0.2	0.3	
		Full range			0.3			0.3	
A_{VD} Large-signal differential voltage amplification	$V_{IC} = 2.5\text{ V}$, $V_O = 1\text{ V to } 4\text{ V}$	$R_L = 50\text{ k}\Omega^\ddagger$	25°C	80	170		80	170	V/mV
			Full range	55			55		
		$R_L = 1\text{ M}\Omega^\ddagger$	25°C	550			550		
$r_{i(d)}$ Differential input resistance		25°C		10^{12}			10^{12}		Ω
$r_{i(c)}$ Common-mode input resistance		25°C		10^{12}			10^{12}		Ω
$C_{i(c)}$ Common-mode input capacitance	$f = 10\text{ kHz}$, N package	25°C		8			8		pF
z_o Closed-loop output impedance	$f = 100\text{ kHz}$, $A_V = 10$	25°C		240			240		Ω
CMRR Common-mode rejection ratio	$V_{IC} = 0\text{ to } 2.7\text{ V}$, $V_O = 2.5\text{ V}$, $R_S = 50\ \Omega$	25°C	70	83		70	83		dB
		Full range	70			70			
k_{SVR} Supply voltage rejection ratio ($\Delta V_{DD}/\Delta V_{IO}$)	$V_{DD} = 4.4\text{ V to } 8\text{ V}$, $V_{IC} = V_{DD}/2$, No load	25°C	80	95		80	95		dB
		Full range	80			80			

† Full range is -40°C to 125°C .

‡ Referenced to 2.5 V

NOTE 4: Typical values are based on the input offset voltage shift observed through 500 hours of operating life test at $T_A = 150^\circ\text{C}$ extrapolated to $T_A = 25^\circ\text{C}$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.



TLV2264I electrical characteristics at specified free-air temperature, $V_{DD} = 5\text{ V}$ (unless otherwise noted) (continued)

PARAMETER	TEST CONDITIONS	$T_A^\dagger$	TLV2264I			TLV2264AI			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
I_{DD} Supply current (four amplifiers)	$V_O = 2.5\text{ V}$, No load	25°C		0.8	1		0.8	1	mA
		Full range			1			1	

† Full range is -40°C to 125°C .

TLV2264I operating characteristics at specified free-air temperature, $V_{DD} = 5\text{ V}$

PARAMETER		TEST CONDITIONS		T _A [†]	TLV2264I			TLV2264AI			UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	
SR	Slew rate at unity gain	V _O = 1.4 V to 2.6 V, R _L = 50 kΩ [‡] , C _L = 100 pF [‡]		25°C	0.35	0.55		0.35	0.55		V/μs
				Full range	0.3			0.3			
V _n	Equivalent input noise voltage	f = 10 Hz		25°C	40			40			nV/√Hz
		f = 1 kHz		25°C	12			12			
V _{N(PP)}	Peak-to-peak equivalent input noise voltage	f = 0.1 Hz to 1 Hz		25°C	0.7			0.7			μV
		f = 0.1 Hz to 10 Hz		25°C	1.3			1.3			
I _n	Equivalent input noise current			25°C	0.6			0.6			fA/√Hz
THD + N	Total harmonic distortion plus noise	V _O = 0.5 V to 2.5 V, f = 20 kHz, R _L = 50 kΩ [‡]	A _V = 1	25°C	0.017%			0.017%			
			A _V = 10		0.03%			0.03%			
	Gain-bandwidth product	f = 50 kHz, R _L = 50 kΩ [‡] , C _L = 100 pF [‡]		25°C	0.71			0.71			MHz
B _{OM}	Maximum output-swing bandwidth	V _{O(PP)} = 2 V, R _L = 50 kΩ [‡] , A _V = 1, C _L = 100 pF [‡]		25°C	185			185			kHz
t _s	Settling time	A _V = −1, Step = 0.5 V to 2.5 V, R _L = 50 kΩ [‡] , C _L = 100 pF [‡]	To 0.1%	25°C	6.4			6.4			μs
			To 0.01%		14.1			14.1			
φ _m	Phase margin at unity gain	R _L = 50 kΩ [‡] , C _L = 100 pF [‡]		25°C	56°			56°			
	Gain margin			25°C	11			11			dB

† Full range is -40°C to 125°C .

‡ Referenced to 2.5 V

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TLV2262Q and TLV2262M electrical characteristics at specified free-air temperature, $V_{DD} = 3\text{ V}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	$T_A^\dagger$	TLV2262Q, TLV2262M			TLV2262AQ, TLV2262AM			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{IO} Input offset voltage	$V_{DD} \pm \pm 1.5\text{ V}, V_{IC} = 0, V_O = 0, R_S = 50\ \Omega$	25°C	300	2500		300	950		μV
		Full range		3000			1500		
α_{VIO} Temperature coefficient of input offset voltage		25°C to 125°C	2			2			$\mu\text{V}/^\circ\text{C}$
Input offset voltage long-term drift (see Note 4)		25°C	0.003			0.003			$\mu\text{V}/\text{mo}$
I_{IO} Input offset current		25°C	0.5	60		0.5	60		pA
		125°C		800			800		
I_{IB} Input bias current		25°C	1	60		1	60		pA
		125°C		800			800		
V_{ICR} Common-mode input voltage range	$R_S = 50\ \Omega, V_{IO} \leq 5\text{ mV}$	25°C	0 to 2	-0.3 to 2.2		0 to 2	-0.3 to 2.2		V
		Full range	0 to 1.7			0 to 1.7			
V_{OH} High-level output voltage	$I_{OH} = -20\ \mu\text{A}$	25°C	2.99			2.99			V
	$I_{OH} = -100\ \mu\text{A}$	25°C	2.85			2.85			
		Full range	2.82			2.82			
	$I_{OH} = -400\ \mu\text{A}$	25°C	2.7			2.7			
		Full range	2.55			2.55			
V_{OL} Low-level output voltage	$V_{IC} = 1.5\text{ V}, I_{OL} = 50\ \mu\text{A}$	25°C	10			10			mV
	$V_{IC} = 1.5\text{ V}, I_{OL} = 500\ \mu\text{A}$	25°C	100	150		100	150		
		Full range		165			165		
	$V_{IC} = 1.5\text{ V}, I_{OL} = 1\text{ mA}$	25°C	200	300		200	300		
		Full range		300			300		
A_{VD} Large-signal differential voltage amplification	$V_{IC} = 1.5\text{ V}, V_O = 1\text{ V to } 2\text{ V}$	$R_L = 50\text{ k}\Omega^\ddagger$	25°C	60	100	60	100		V/mV
		$R_L = 1\text{ M}\Omega^\ddagger$	Full range	25		25			
			25°C	100		100			
$r_{i(d)}$ Differential input resistance		25°C	10^{12}			10^{12}			Ω
$r_{i(c)}$ Common-mode input resistance		25°C	10^{12}			10^{12}			Ω
$C_{i(c)}$ Common-mode input capacitance	$f = 10\text{ kHz}, \text{ P package}$	25°C	8			8			pF
z_o Closed-loop output impedance	$f = 100\text{ kHz}, A_V = 10$	25°C	270			270			Ω
CMRR Common-mode rejection ratio	$V_{IC} = 0\text{ to } 1.7\text{ V}, V_O = 1.5\text{ V}, R_S = 50\ \Omega$	25°C	65	75		65	77		dB
		Full range	60			60			
k_{SVR} Supply voltage rejection ratio ($\Delta V_{DD}/\Delta V_{IO}$)	$V_{DD} = 2.7\text{ V to } 8\text{ V}, V_{IC} = V_{DD}/2, \text{ No load}$	25°C	80	95		80	100		dB
		Full range	80			80			

† Full range is -40°C to 125°C for Q level part, -55°C to 125°C for M level part.

‡ Referenced to 1.5 V

NOTE 4: Typical values are based on the input offset voltage shift observed through 500 hours of operating life test at $T_A = 150^\circ\text{C}$ extrapolated to $T_A = 25^\circ\text{C}$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.



TLV2262Q and TLV2262M electrical characteristics at specified free-air temperature, $V_{DD} = 3\text{ V}$ (unless otherwise noted) (continued)

PARAMETER	TEST CONDITIONS	$T_A^\dagger$	TLV2262Q, TLV2262M			TLV2262AQ, TLV2262AM			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
I_{DD} Supply current	$V_O = 1.5\text{ V}$, No load	25°C		400	500		400	500	μA
		Full range			500			500	

† Full range is -40°C to 125°C for Q level part, -55°C to 125°C for M level part.

TLV2262Q and TLV2262M operating characteristics at specified free-air temperature, $V_{DD} = 3\text{ V}$

PARAMETER	TEST CONDITIONS	$T_A^\dagger$	TLV2262Q, TLV2262M			TLV2262AQ, TLV2262AM			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
SR Slew rate at unity gain	$V_O = 0.5\text{ V}$ to 1.7 V , $R_L = 50\text{ k}\Omega^\ddagger$, $C_L = 100\text{ pF}^\ddagger$	25°C	0.35	0.55		0.35	0.55		$\text{V}/\mu\text{s}$
		Full range	0.25			0.25			
V_n Equivalent input noise voltage	$f = 10\text{ Hz}$	25°C		43			43		$\text{nV}/\sqrt{\text{Hz}}$
	$f = 1\text{ kHz}$	25°C		12			12		
$V_{N(PP)}$ Peak-to-peak equivalent input noise voltage	$f = 0.1\text{ Hz}$ to 1 Hz	25°C		0.6			0.6		μV
	$f = 0.1\text{ Hz}$ to 10 Hz	25°C		1			1		
I_n Equivalent input noise current		25°C		0.6			0.6		$\text{fA}/\sqrt{\text{Hz}}$
THD + N Total harmonic distortion plus noise	$V_O = 0.5\text{ V}$ to 2.5 V , $f = 20\text{ kHz}$, $R_L = 50\text{ k}\Omega^\ddagger$	$A_V = 1$		0.03%			0.03%		
		$A_V = 10$		0.05%			0.05%		
Gain-bandwidth product	$f = 1\text{ kHz}$, $R_L = 50\text{ k}\Omega^\ddagger$, $C_L = 100\text{ pF}^\ddagger$	25°C		0.67			0.67		MHz
B_{OM} Maximum output-swing bandwidth	$V_{O(PP)} = 1\text{ V}$, $R_L = 50\text{ k}\Omega^\ddagger$, $A_V = 1$, $C_L = 100\text{ pF}^\ddagger$	25°C		395			395		kHz
t_s Settling time	$A_V = -1$, Step = 1 V to 2 V , $R_L = 50\text{ k}\Omega^\ddagger$, $C_L = 100\text{ pF}^\ddagger$	$T_o = 0.1\%$		5.6			5.6		μs
		$T_o = 0.01\%$		12.5			12.5		
ϕ_m Phase margin at unity gain	$R_L = 50\text{ k}\Omega^\ddagger$, $C_L = 100\text{ pF}^\ddagger$	25°C		55°			55°		
Gain margin		25°C		11			11		dB

† Full range is -40°C to 125°C for Q level part, -55°C to 125°C for M level part.

‡ Referenced to 1.5 V

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TLV2262Q and TLV2262M electrical characteristics at specified free-air temperature, $V_{DD} = 5\text{ V}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	$T_A^\dagger$	TLV2262Q, TLV2262M			TLV2262AQ, TLV2262AM			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{IO} Input offset voltage	$V_{DD} \pm \pm 2.5\text{ V}, V_{IC} = 0, V_O = 0, R_S = 50\ \Omega$	25°C	300	2500		300	950		μV
		Full range		3000			1500		
α_{VIO} Temperature coefficient of input offset voltage		25°C to 125°C	2			2			$\mu\text{V}/^\circ\text{C}$
Input offset voltage long-term drift (see Note 4)		25°C	0.003			0.003			$\mu\text{V}/\text{mo}$
I_{IO} Input offset current		25°C	0.5	60		0.5	60		pA
		125°C		800			800		
I_{IB} Input bias current		25°C	1	60		1	60		pA
		125°C		800			800		
V_{ICR} Common-mode input voltage range	$ V_{IO} \leq 5\text{ mV}, R_S = 50\ \Omega$	25°C	0 to 4	-0.3 to 4.2		0 to 4	-0.3 to 4.2		V
		Full range	0 to 3.5			0 to 3.5			
V_{OH} High-level output voltage	$I_{OH} = -20\ \mu\text{A}$	25°C		4.99			4.99		V
	$I_{OH} = -100\ \mu\text{A}$	25°C	4.85	4.94		4.85	4.94		
		Full range	4.82			4.82			
	$I_{OH} = -400\ \mu\text{A}$	25°C	4.7	4.85		4.7	4.85		
		Full range	4.5			4.5			
V_{OL} Low-level output voltage	$V_{IC} = 2.5\text{ V}, I_{OL} = 50\ \mu\text{A}$	25°C		0.01			0.01		V
	$V_{IC} = 2.5\text{ V}, I_{OL} = 500\ \mu\text{A}$	25°C		0.09 0.15			0.09 0.15		
		Full range		0.15			0.15		
	$V_{IC} = 2.5\text{ V}, I_{OL} = 1\text{ mA}$	25°C		0.2 0.3			0.2 0.3		
		Full range		0.3			0.3		
A_{VD} Large-signal differential voltage amplification	$V_{IC} = 2.5\text{ V}, V_O = 1\text{ V to }4\text{ V}$	$R_L = 50\text{ k}\Omega^\ddagger$	25°C	80	170		80	170	V/mV
			Full range	50			50		
		$R_L = 1\text{ M}\Omega^\ddagger$	25°C	550			550		
$r_{i(d)}$ Differential input resistance		25°C		10^{12}			10^{12}		Ω
$r_{i(c)}$ Common-mode input resistance		25°C		10^{12}			10^{12}		Ω
$c_{i(c)}$ Common-mode input capacitance	$f = 10\text{ kHz}, \text{ P package}$	25°C		8			8		pF
z_o Closed-loop output impedance	$f = 100\text{ kHz}, A_V = 10$	25°C		240			240		Ω
CMRR Common-mode rejection ratio	$V_{IC} = 0\text{ to }2.7\text{ V}, V_O = 2.5\text{ V}, R_S = 50\ \Omega$	25°C	70	83		70	83		dB
		Full range	70			70			
k_{SVR} Supply voltage rejection ratio ($\Delta V_{DD}/\Delta V_{IO}$)	$V_{DD} = 4.4\text{ V to }8\text{ V}, V_{IC} = V_{DD}/2, \text{ No load}$	25°C	80	95		80	95		dB
		Full range	80			80			

† Full range is -40°C to 125°C for Q level part, -55°C to 125°C for M level part.

‡ Referenced to 2.5 V

NOTE 4: Typical values are based on the input offset voltage shift observed through 500 hours of operating life test at $T_A = 150^\circ\text{C}$ extrapolated to $T_A = 25^\circ\text{C}$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.



TLV2262Q and TLV2262M electrical characteristics at specified free-air temperature, $V_{DD} = 5\text{ V}$ (unless otherwise noted) (continued)

PARAMETER	TEST CONDITIONS	$T_A^\dagger$	TLV2262Q, TLV2262M			TLV2262AQ, TLV2262AM			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
I_{DD} Supply current	$V_O = 2.5\text{ V}$, No load	25°C	400	500		400	500		μA
		Full range		500			500		

† Full range is -40°C to 125°C for Q level part, -55°C to 125°C for M level part.

TLV2262Q and TLV2262M operating characteristics at specified free-air temperature, $V_{DD} = 5\text{ V}$

PARAMETER		TEST CONDITIONS		T _A [†]	TLV2262Q, TLV2262M			TLV2262AQ, TLV2262AM			UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	
SR	Slew rate at unity gain	V _O = 0.5 V to 3.5 V, R _L = 50 kΩ [‡] C _L = 100 pF [‡]		25°C	0.35	0.55		0.35	0.55		V/μs
				Full range	0.25			0.25			
V _n	Equivalent input noise voltage	f = 10 Hz		25°C	40			40			nV/√Hz
		f = 1 kHz		25°C	12			12			
V _{N(PP)}	Peak-to-peak equivalent input noise voltage	f = 0.1 Hz to 1 Hz		25°C	0.7			0.7			μV
		f = 0.1 Hz to 10 Hz		25°C	1.3			1.3			
I _n	Equivalent input noise current			25°C	0.6			0.6			fA/√Hz
THD + N	Total harmonic distortion plus noise	V _O = 0.5 V to 2.5 V, f = 20 kHz, R _L = 50 kΩ [‡]	A _V = 1	25°C	0.017%			0.017%			
			A _V = 10		0.03%			0.03%			
	Gain-bandwidth product	f = 50 kHz, R _L = 50 kΩ [‡] , C _L = 100 pF [‡]		25°C	0.71			0.71			MHz
B _{OM}	Maximum output-swing bandwidth	V _{O(PP)} = 2 V, R _L = 50 kΩ [‡] ,	A _V = 1, C _L = 100 pF [‡]	25°C	185			185			kHz
t _s	Settling time	A _V = −1, Step = 0.5 V to 2.5 V, R _L = 50 kΩ [‡] , C _L = 100 pF [‡]	To 0.1%	25°C	6.4			6.4			μs
			To 0.01%		14.1			14.1			
φ _m	Phase margin at unity gain	R _L = 50 kΩ [‡] , C _L = 100 pF [‡]		25°C	56°			56°			
	Gain margin			25°C	11			11			dB

† Full range is -40°C to 125°C for Q level part, -55°C to 125°C for M level part.

‡ Referenced to 2.5 V

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TLV2264Q and TLV2264M electrical characteristics at specified free-air temperature, $V_{DD} = 3\text{ V}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	$T_A^\dagger$	TLV2264Q, TLV2264M			TLV2264AQ, TLV2264AM			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{IO} Input offset voltage	$V_{DD} \pm \pm 1.5\text{ V}$, $V_{IC} = 0$, $V_O = 0$, $R_S = 50\ \Omega$	25°C		300	2500		300	950	μV
		Full range			3000			1500	
α_{VIO} Temperature coefficient of input offset voltage		25°C to 125°C		2			2		$\mu\text{V}/^\circ\text{C}$
Input offset voltage long-term drift (see Note 4)		25°C		0.003			0.003		$\mu\text{V}/\text{mo}$
I_{IO} Input offset current		25°C		0.5	60		0.5	60	pA
		125°C			800			800	
I_{IB} Input bias current		25°C		1	60		1	60	pA
		125°C			800			800	
V_{ICR} Common-mode input voltage range	$R_S = 50\ \Omega$, $ V_{IO} \leq 5\text{ mV}$	25°C	0 to 2	-0.3 to 2.2		0 to 2	-0.3 to 2.2		V
		Full range	0 to 1.7			0 to 1.7			
V_{OH} High-level output voltage	$I_{OH} = -20\ \mu\text{A}$	25°C		2.99			2.99		V
	$I_{OH} = -100\ \mu\text{A}$	25°C		2.85			2.85		
		Full range		2.82			2.82		
	$I_{OH} = -400\ \mu\text{A}$	25°C		2.7			2.7		
V_{OL} Low-level output voltage	$V_{IC} = 1.5\text{ V}$, $I_{OL} = 50\ \mu\text{A}$	25°C		10			10		mV
	$V_{IC} = 1.5\text{ V}$, $I_{OL} = 500\ \mu\text{A}$	25°C		100	150		100	150	
		Full range			150			150	
	$V_{IC} = 1.5\text{ V}$, $I_{OL} = 1\text{ mA}$	25°C		200	300		200	300	
A_{VD} Large-signal differential voltage amplification	$V_{IC} = 1.5\text{ V}$, $V_O = 1\text{ V to }2\text{ V}$	$R_L = 50\text{ k}\Omega^\ddagger$	25°C	60	100		60	100	V/mV
			Full range	25			25		
		$R_L = 1\text{ M}\Omega^\ddagger$	25°C	100			100		
$r_{i(d)}$ Differential input resistance		25°C		10^{12}			10^{12}		Ω
$r_{i(c)}$ Common-mode input resistance		25°C		10^{12}			10^{12}		Ω
$C_{i(c)}$ Common-mode input capacitance	$f = 10\text{ kHz}$, N package	25°C		8			8		pF
z_o Closed-loop output impedance	$f = 100\text{ kHz}$, $A_V = 10$	25°C		270			270		Ω
CMRR Common-mode rejection ratio	$V_{IC} = 0\text{ to }1.7\text{ V}$, $V_O = 1.5\text{ V}$, $R_S = 50\ \Omega$	25°C	65	75		65	77		dB
		Full range	60			60			
k_{SVR} Supply voltage rejection ratio ($\Delta V_{DD}/\Delta V_{IO}$)	$V_{DD} = 2.7\text{ V to }8\text{ V}$, $V_{IC} = V_{DD}/2$, No load	25°C	80	95		80	100		dB
		Full range	80			80			

† Full range is -40°C to 125°C for Q level part, -55°C to 125°C for M level part.

‡ Referenced to 1.5 V

NOTE 4: Typical values are based on the input offset voltage shift observed through 500 hours of operating life test at $T_A = 150^\circ\text{C}$ extrapolated to $T_A = 25^\circ\text{C}$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.

TLV2264Q and TLV2264M electrical characteristics at specified free-air temperature, $V_{DD} = 3\text{ V}$ (unless otherwise noted) (continued)

PARAMETER		TEST CONDITIONS		T _A [†]	TLV2264Q, TLV2264M			TLV2264AQ, TLV2264AM			UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	
I _{DD}	Supply current (four amplifiers)	V _O = 1.5 V,	No load	25°C	0.8			0.8			mA
				Full range	1			1			

† Full range is -40°C to 125°C for Q level part, -55°C to 125°C for M level part.

TLV2264Q and TLV2264M operating characteristics at specified free-air temperature, $V_{DD} = 3\text{ V}$

PARAMETER		TEST CONDITIONS		T _A [†]	TLV2264Q, TLV2264M			TLV2264AQ, TLV2264AM			UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	
SR	Slew rate at unity gain	V _O = 0.5 V to 1.7 V, R _L = 50 kΩ [‡] , C _L = 100 pF [‡]		25°C	0.35	0.55		0.35	0.55		V/μs
				Full range	0.25			0.25			
V _n	Equivalent input noise voltage	f = 10 Hz		25°C	43			43			nV/√Hz
		f = 1 kHz		25°C	12			12			
V _{N(PP)}	Peak-to-peak equivalent input noise voltage	f = 0.1 Hz to 1 Hz		25°C	0.6			0.6			μV
		f = 0.1 Hz to 10 Hz		25°C	1			1			
I _n	Equivalent input noise current			25°C	0.6			0.6			fA/√Hz
THD + N	Total harmonic distortion plus noise	V _O = 0.5 V to 2.5 V, f = 20 kHz, R _L = 50 kΩ [‡]		25°C	A _V = 1			0.03%			
		A _V = 10			0.05%						
	Gain-bandwidth product	f = 1 kHz, R _L = 50 kΩ [‡] , C _L = 100 pF [‡]		25°C	0.67			0.67			MHz
B _{OM}	Maximum output-swing bandwidth	V _{O(PP)} = 1 V, R _L = 50 kΩ [‡] , C _L = 100 pF [‡]		25°C	395			395			kHz
t _s	Settling time	A _V = −1, Step = 1 V to 2 V, R _L = 50 kΩ [‡] , C _L = 100 pF [‡]		25°C	5.6			5.6			μs
					12.5			12.5			
φ _m	Phase margin at unity gain	R _L = 50 kΩ [‡] , C _L = 100 pF [‡]		25°C	55°			55°			
	Gain margin			25°C	11			11			dB

† Full range is -40°C to 125°C for Q level part, -55°C to 125°C for M level part.

‡ Referenced to 1.5 V

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TLV2264Q and TLV2264M electrical characteristics at specified free-air temperature, $V_{DD} = 5\text{ V}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	$T_A^\dagger$	TLV2264Q, TLV2264M			TLV2264AQ, TLV2264AM			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{IO} Input offset voltage	$V_{DD} \pm \pm 2.5\text{ V}$, $V_{IC} = 0$, $V_O = 0$, $R_S = 50\ \Omega$	25°C		300	2500		300	950	μV
		Full range			3000			1500	
α_{VIO} Temperature coefficient of input offset voltage		25°C to 125°C		2			2		$\mu\text{V}/^\circ\text{C}$
Input offset voltage long-term drift (see Note 4)		25°C		0.003			0.003		$\mu\text{V}/\text{mo}$
I_{IO} Input offset current		25°C		0.5	60		0.5	60	pA
		125°C			800			800	
I_{IB} Input bias current		25°C		1	60		1	60	pA
		125°C			800			800	
V_{ICR} Common-mode input voltage range	$ V_{IO} \leq 5\text{ mV}$, $R_S = 50\ \Omega$	25°C	0 to 4	-0.3 to 4.2		0 to 4	-0.3 to 4.2		V
		Full range	0 to 3.5			0 to 3.5			
V_{OH} High-level output voltage	$I_{OH} = -20\ \mu\text{A}$	25°C		4.99			4.99		V
	$I_{OH} = -100\ \mu\text{A}$	25°C		4.85	4.94		4.85	4.94	
		Full range		4.82			4.82		
	$I_{OH} = -400\ \mu\text{A}$	25°C		4.7	4.85		4.7	4.85	
V_{OL} Low-level output voltage	$V_{IC} = 2.5\text{ V}$, $I_{OL} = 50\ \mu\text{A}$	25°C		0.01			0.01		V
	$V_{IC} = 2.5\text{ V}$, $I_{OL} = 500\ \mu\text{A}$	25°C		0.09	0.15		0.09	0.15	
		Full range			0.15			0.15	
	$V_{IC} = 2.5\text{ V}$, $I_{OL} = 1\text{ mA}$	25°C		0.2	0.3		0.2	0.3	
A_{VD} Large-signal differential voltage amplification	$V_{IC} = 2.5\text{ V}$, $V_O = 1\text{ V to } 4\text{ V}$	$R_L = 50\text{ k}\Omega^\ddagger$	25°C	80	170		80	170	V/mV
			Full range	50			50		
		$R_L = 1\text{ M}\Omega^\ddagger$	25°C		550			550	
$r_{i(d)}$ Differential input resistance		25°C		10^{12}			10^{12}		Ω
$r_{i(c)}$ Common-mode input resistance		25°C		10^{12}			10^{12}		Ω
$C_{i(c)}$ Common-mode input capacitance	$f = 10\text{ kHz}$, N package	25°C		8			8		pF
z_o Closed-loop output impedance	$f = 100\text{ kHz}$, $A_V = 10$	25°C		240			240		Ω
CMRR Common-mode rejection ratio	$V_{IC} = 0\text{ to } 2.7\text{ V}$, $V_O = 2.5\text{ V}$, $R_S = 50\ \Omega$	25°C		70	83		70	83	dB
		Full range		70			70		
k_{SVR} Supply voltage rejection ratio ($\Delta V_{DD}/\Delta V_{IO}$)	$V_{DD} = 4.4\text{ V to } 8\text{ V}$, $V_{IC} = V_{DD}/2$, No load	25°C		80	95		80	95	dB
		Full range		80			80		

† Full range is -40°C to 125°C for Q level part, -55°C to 125°C for M level part.

‡ Referenced to 2.5 V

NOTE 4: Typical values are based on the input offset voltage shift observed through 500 hours of operating life test at $T_A = 150^\circ\text{C}$ extrapolated to $T_A = 25^\circ\text{C}$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.



TLV2264Q and TLV2264M electrical characteristics at specified free-air temperature, $V_{DD} = 5\text{ V}$ (unless otherwise noted) (continued)

PARAMETER		TEST CONDITIONS		T _A [†]	TLV2264Q, TLV2264M			TLV2264AQ, TLV2264AM			UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	
I _{DD}	Supply current (four amplifiers)	V _O = 2.5 V,	No load	25°C	0.8		1	0.8		1	mA
				Full range			1	1			

† Full range is -40°C to 125°C for Q level part, -55°C to 125°C for M level part.

TLV2264Q and TLV2264M operating characteristics at specified free-air temperature, $V_{DD} = 5\text{ V}$

PARAMETER		TEST CONDITIONS		T _A [†]	TLV2264Q, TLV2264M			TLV2264AQ, TLV2264AM			UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	
SR	Slew rate at unity gain	V _O = 0.5 V to 3.5 V, R _L = 50 kΩ [‡] , C _L = 100 pF [‡]		25°C	0.35	0.55		0.35	0.55		V/μs
				Full range	0.25			0.25			
V _n	Equivalent input noise voltage	f = 10 Hz		25°C	40			40			nV/√Hz
		f = 1 kHz		25°C	12			12			
V _{N(PP)}	Peak-to-peak equivalent input noise voltage	f = 0.1 Hz to 1 Hz		25°C	0.7			0.7			μV
		f = 0.1 Hz to 10 Hz		25°C	1.3			1.3			
I _n	Equivalent input noise current			25°C	0.6			0.6			fA/√Hz
THD + N	Total harmonic distortion plus noise	V _O = 0.5 V to 2.5 V, f = 20 kHz, R _L = 50 kΩ [‡]		25°C	0.017%			0.017%			
		A _V = 10			0.03%			0.03%			
	Gain-bandwidth product	f = 50 kHz, R _L = 50 kΩ [‡] , C _L = 100 pF [‡]		25°C	0.71			0.71			MHz
B _{OM}	Maximum output-swing bandwidth	V _{O(PP)} = 2 V, R _L = 50 kΩ [‡] , A _V = 1, C _L = 100 pF [‡]		25°C	185			185			kHz
t _s	Settling time	A _V = −1, Step = 0.5 V to 2.5 V, R _L = 50 kΩ [‡] , C _L = 100 pF [‡]		25°C	6.4			6.4			μs
					14.1			14.1			
φ _m	Phase margin at unity gain	R _L = 50 kΩ [‡] , C _L = 100 pF [‡]		25°C	56°			56°			
	Gain margin			25°C	11			11			dB

† Full range is -40°C to 125°C for Q level part, -55°C to 125°C for M level part.

‡ Referenced to 2.5 V

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DISTRIBUTION OF TLV2262
INPUT OFFSET VOLTAGE

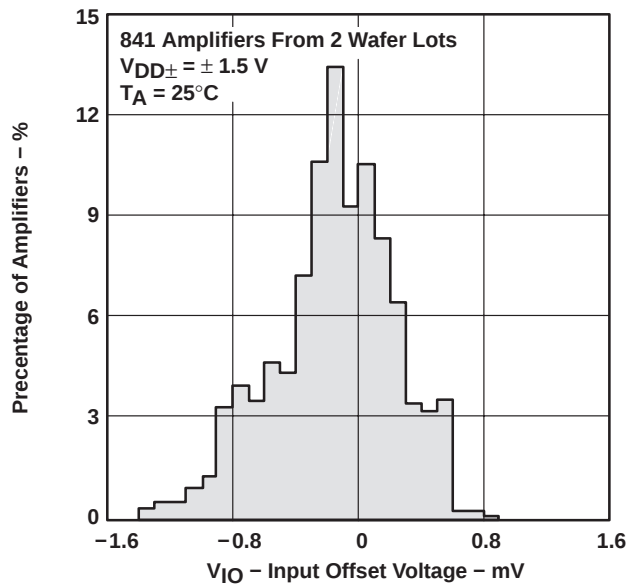


Figure 2

DISTRIBUTION OF TLV2262
INPUT OFFSET VOLTAGE

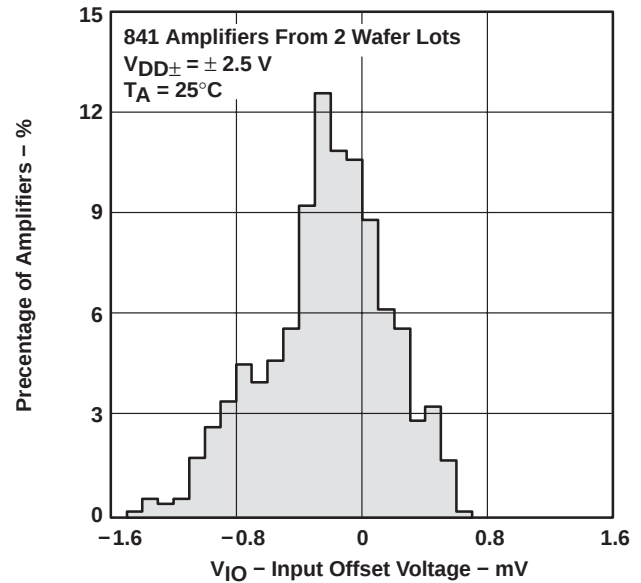


Figure 3

DISTRIBUTION OF TLV2264
INPUT OFFSET VOLTAGE

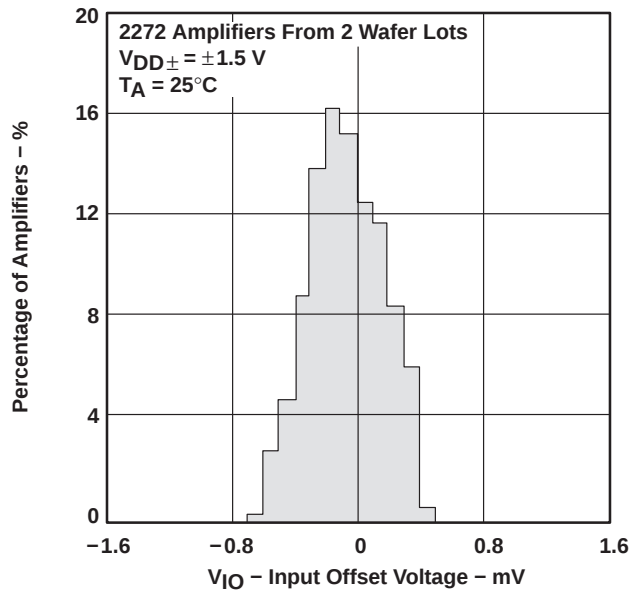


Figure 4

DISTRIBUTION OF TLV2264
INPUT OFFSET VOLTAGE

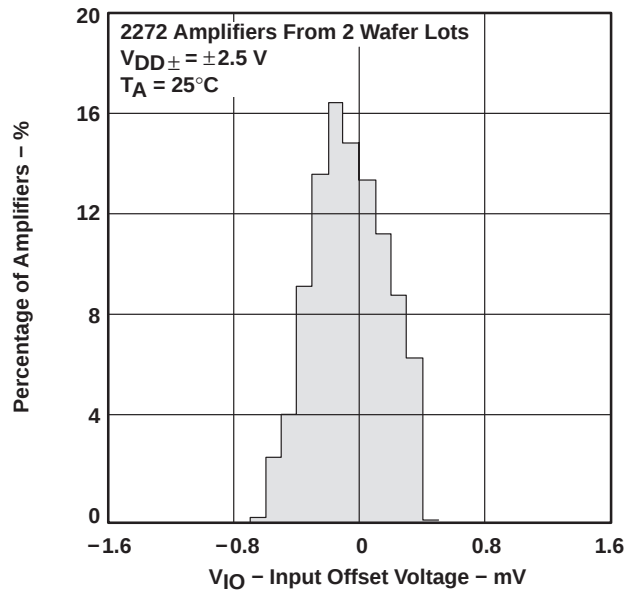


Figure 5

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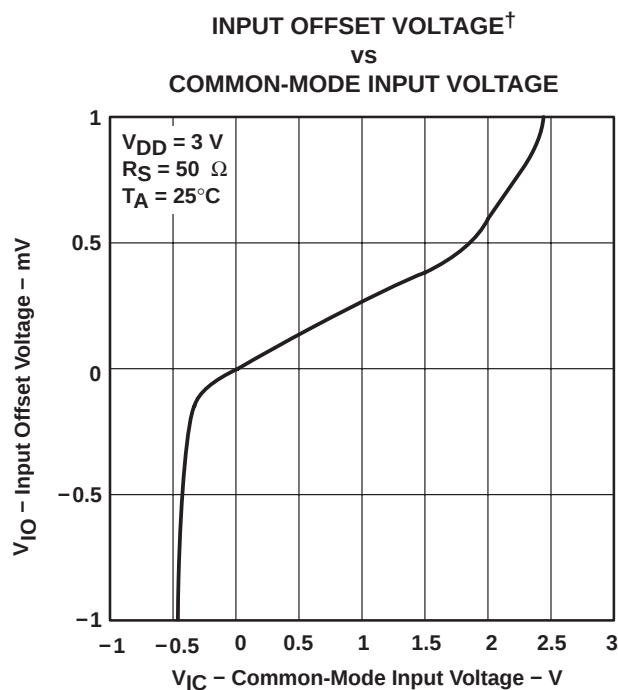


Figure 6

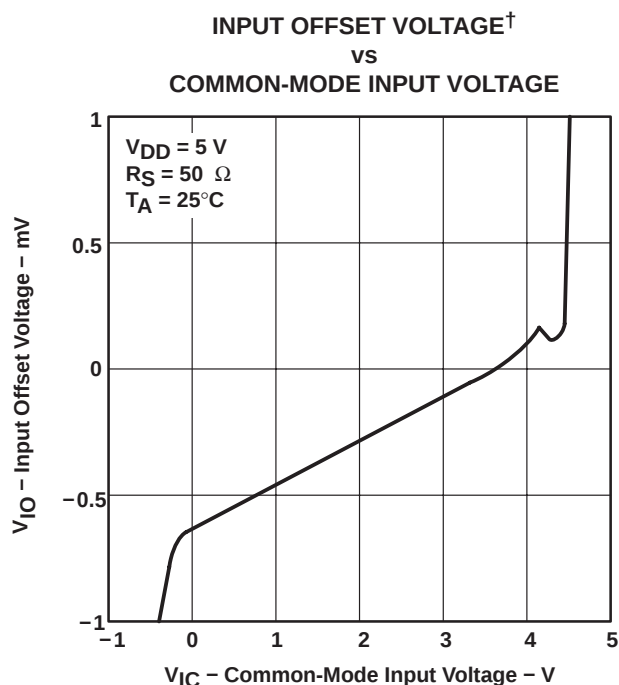


Figure 7

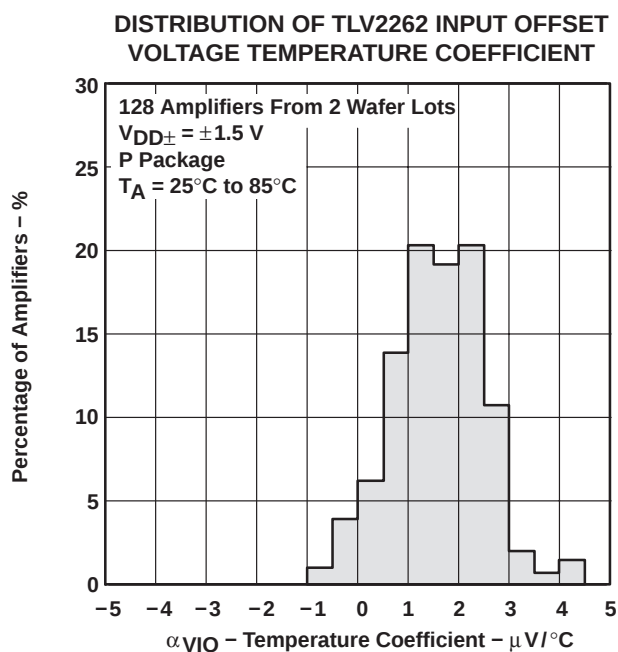


Figure 8

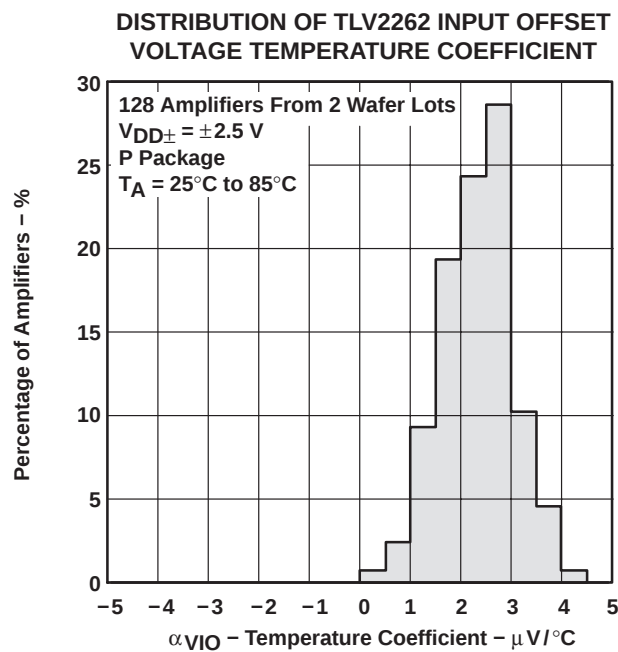


Figure 9

[†] For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V . For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V .

TYPICAL CHARACTERISTICS



Figure 10



Figure 11



Figure 12

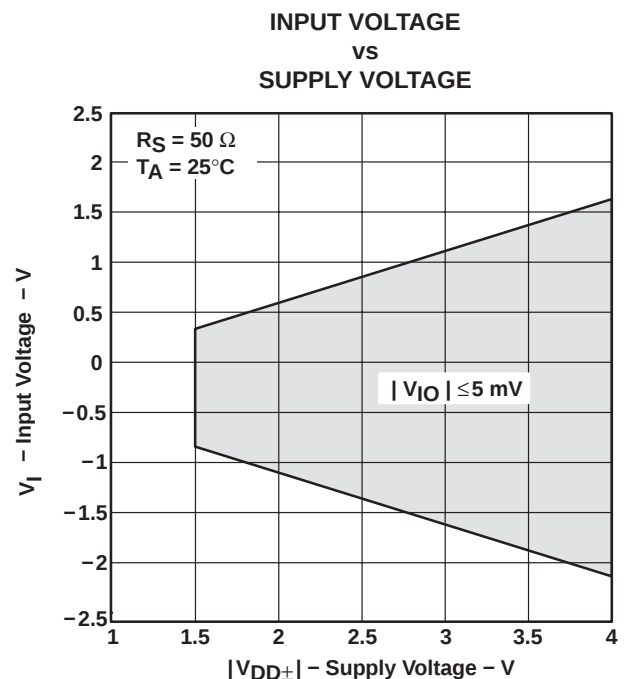


Figure 13

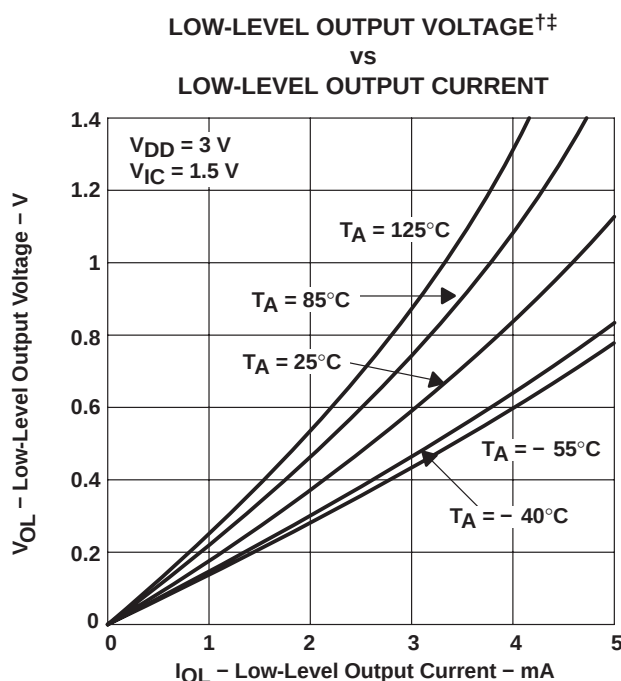
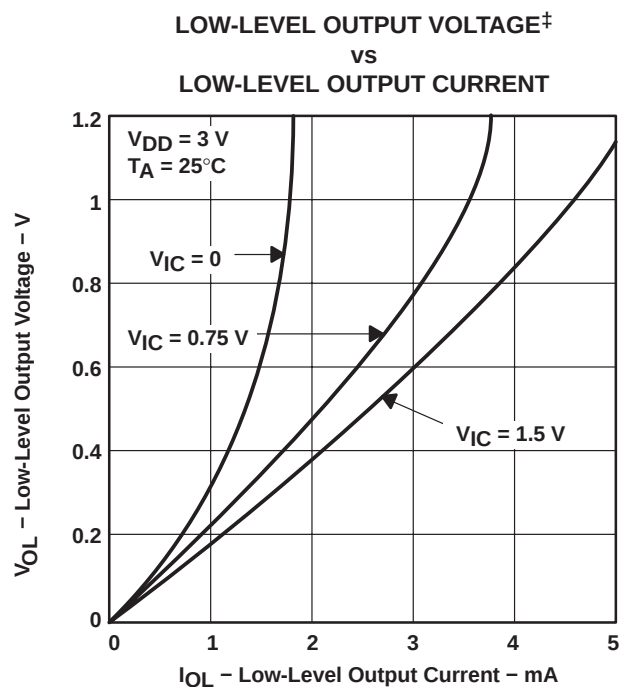
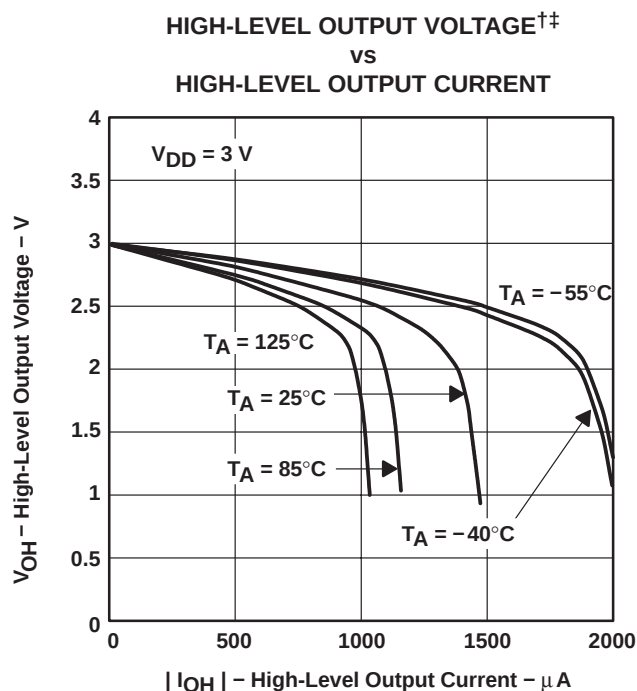
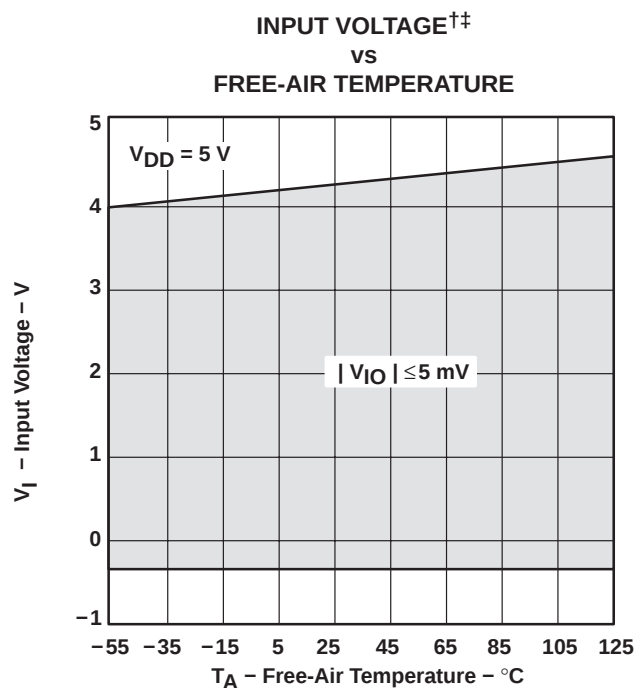
† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

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[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

[‡] For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V . For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V .

TYPICAL CHARACTERISTICS



Figure 18



Figure 19



Figure 20

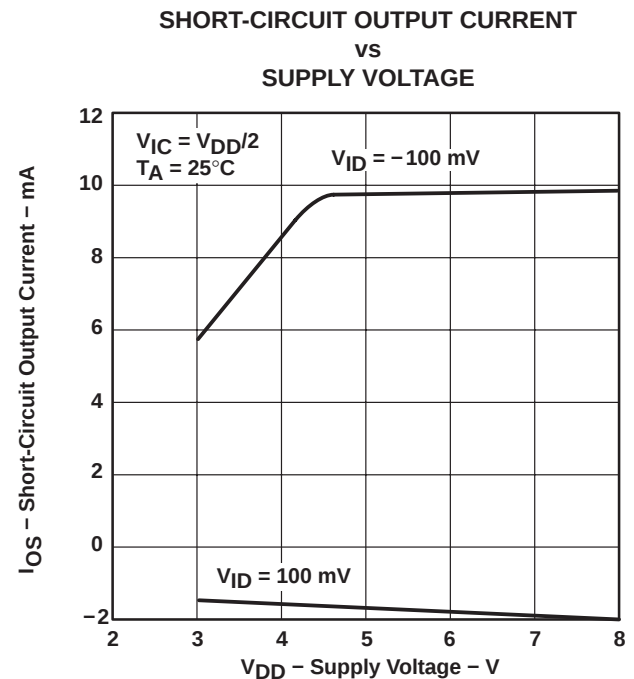


Figure 21

[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

[‡] For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V.

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Figure 22



Figure 23

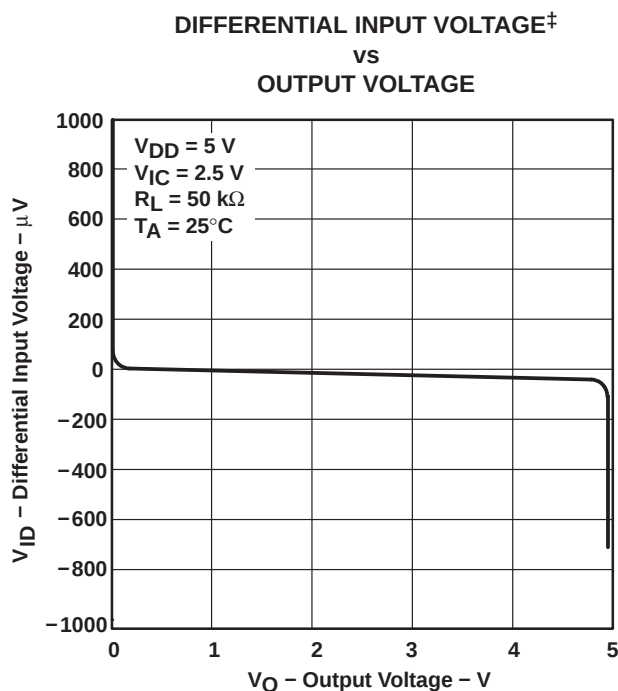


Figure 24

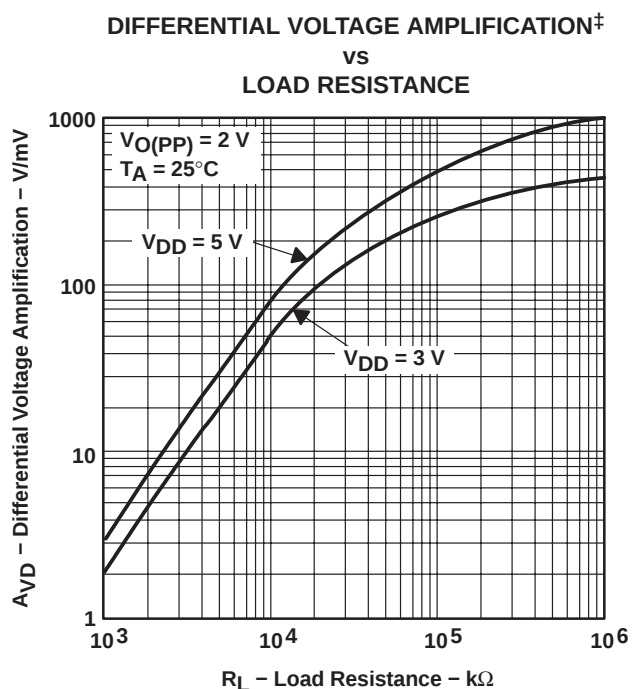


Figure 25

[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

[‡] For all curves where $V_{DD} = 5 \text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3 \text{ V}$, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE MARGIN† vs FREQUENCY



Figure 26

LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE MARGIN† vs FREQUENCY



Figure 27

† For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V.

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TYPICAL CHARACTERISTICS



Figure 28

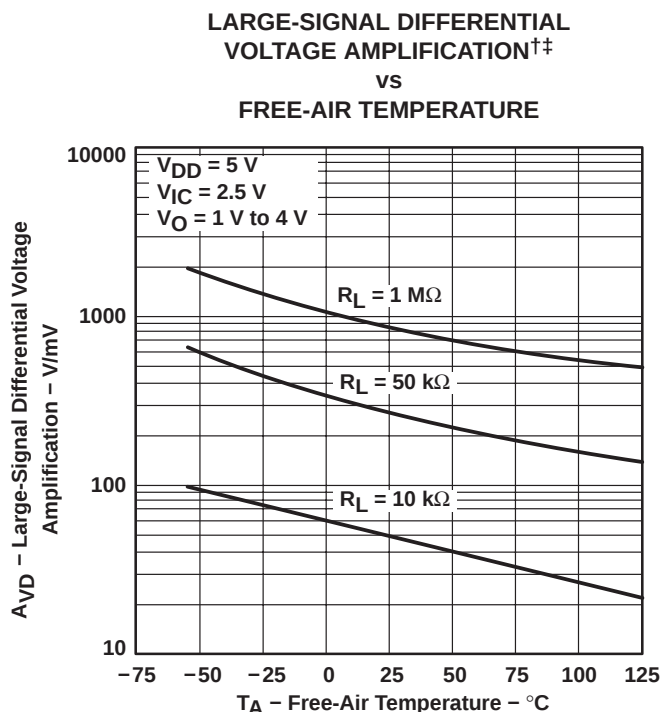


Figure 29



Figure 30

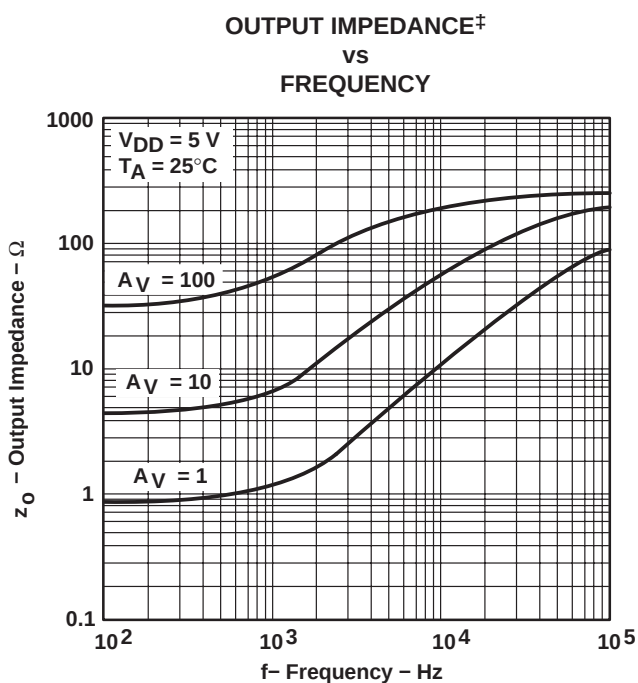


Figure 31

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

‡ For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

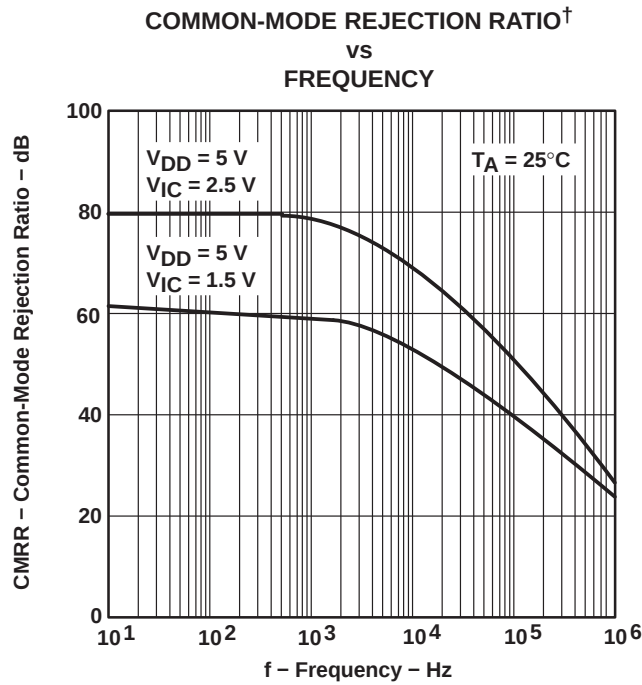


Figure 32

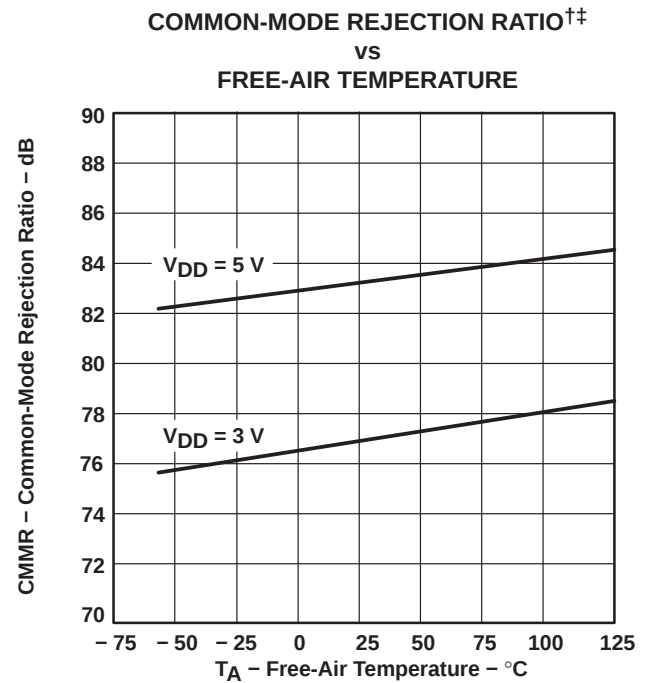


Figure 33



Figure 34

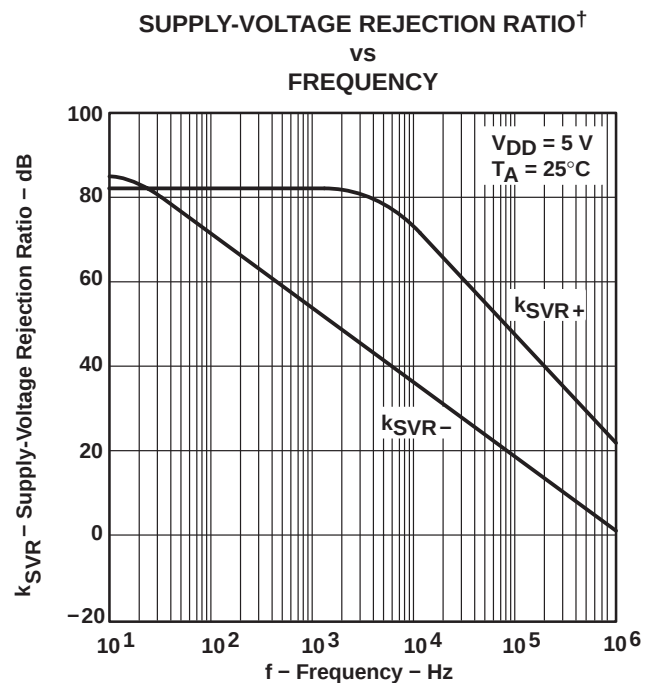


Figure 35

[†] For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V.

^{††} Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

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TYPICAL CHARACTERISTICS



Figure 36



Figure 37



Figure 38

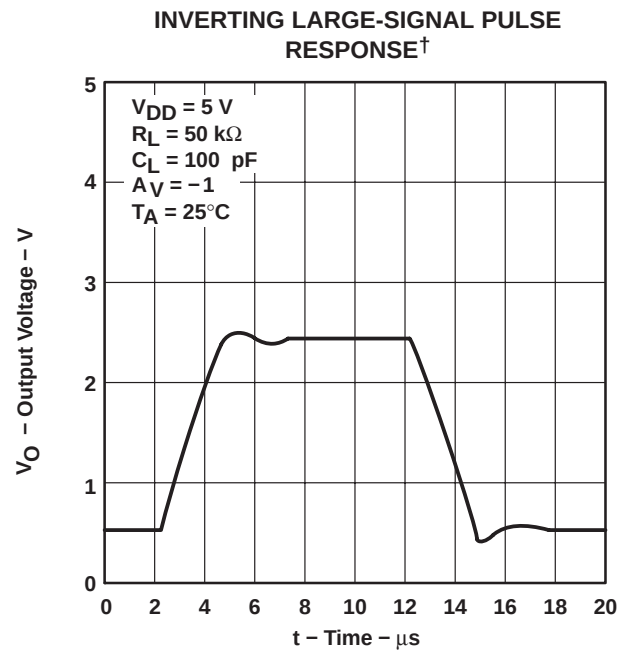
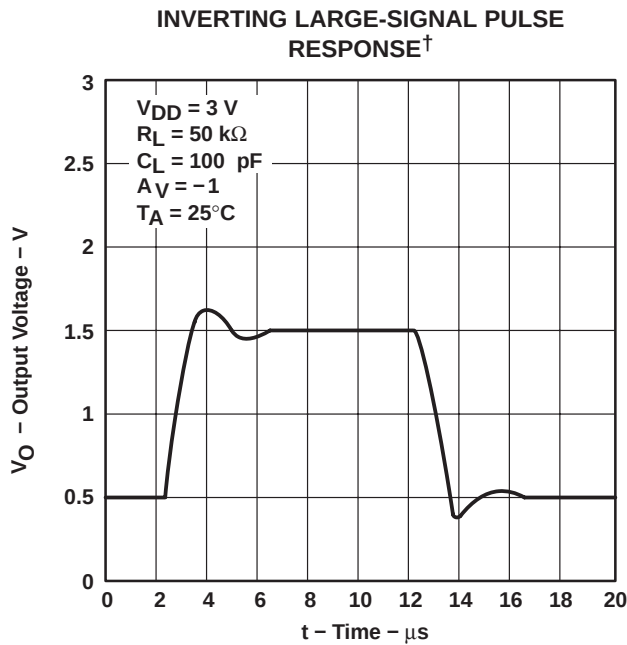
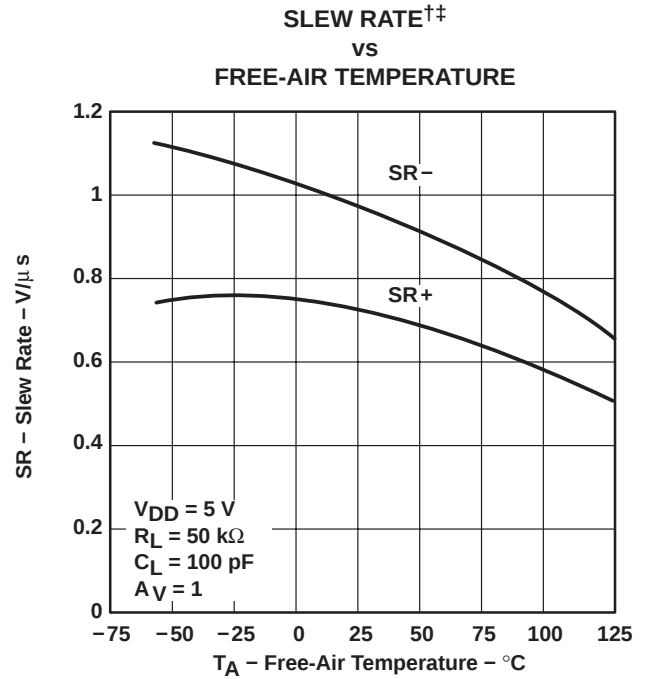
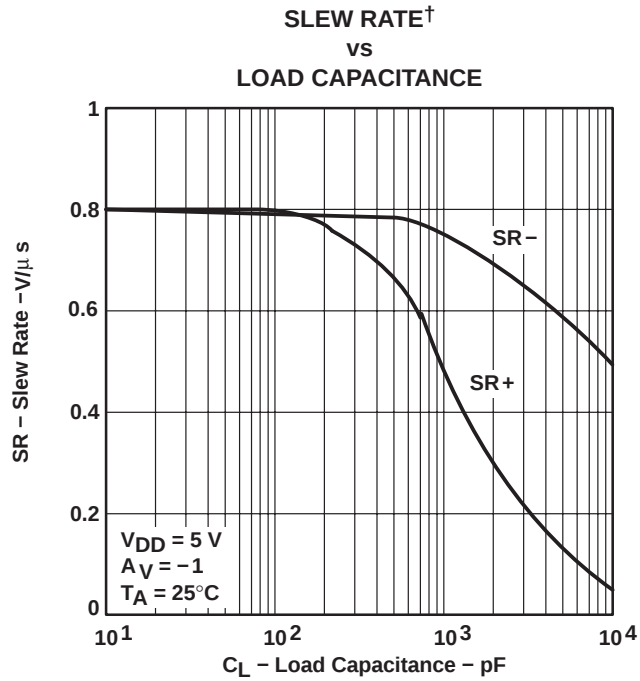


Figure 39

[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

[‡] For all curves where $V_{DD} = 5 \text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3 \text{ V}$, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS



[†] For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V.

^{††} Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

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TYPICAL CHARACTERISTICS

VOLTAGE-FOLLOWER LARGE-SIGNAL
PULSE RESPONSE†



Figure 44

VOLTAGE-FOLLOWER LARGE-SIGNAL
PULSE RESPONSE†



Figure 45

INVERTING SMALL-SIGNAL
PULSE RESPONSE†

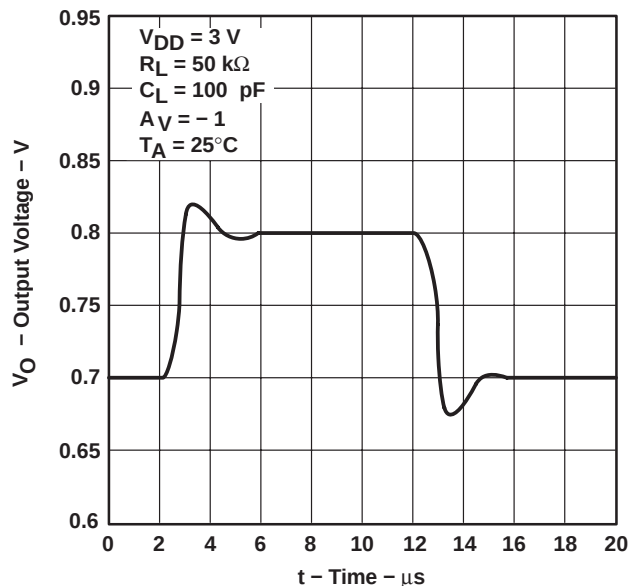


Figure 46

INVERTING SMALL-SIGNAL
PULSE RESPONSE†

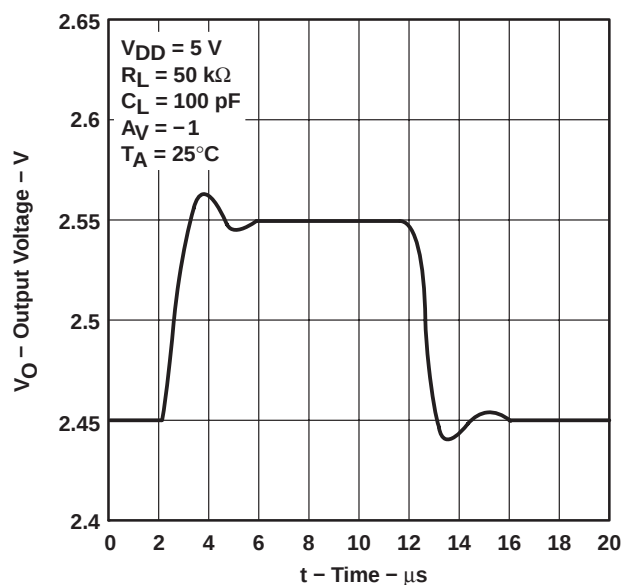


Figure 47

† For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS



Figure 48



Figure 49

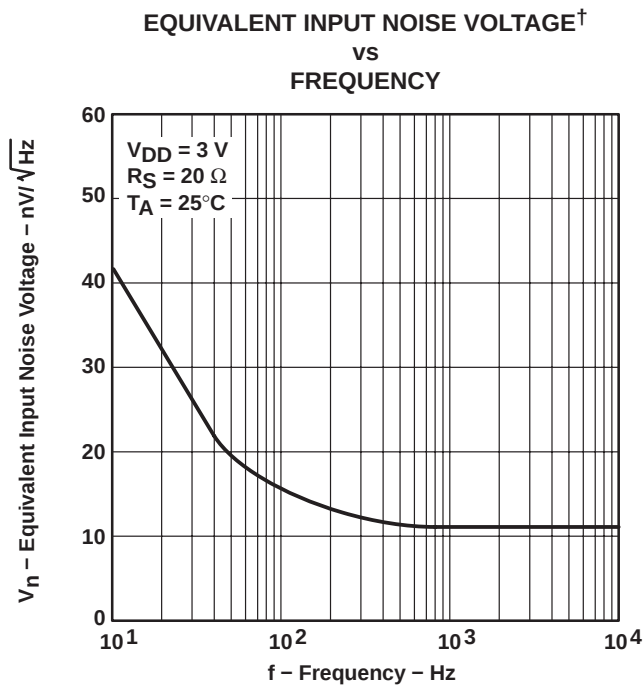


Figure 50



Figure 51

† For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V.

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TYPICAL CHARACTERISTICS



Figure 52

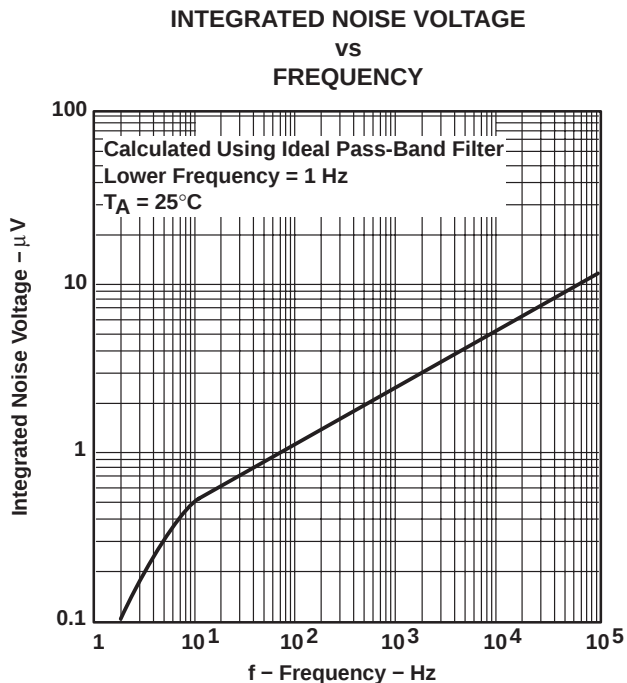


Figure 53

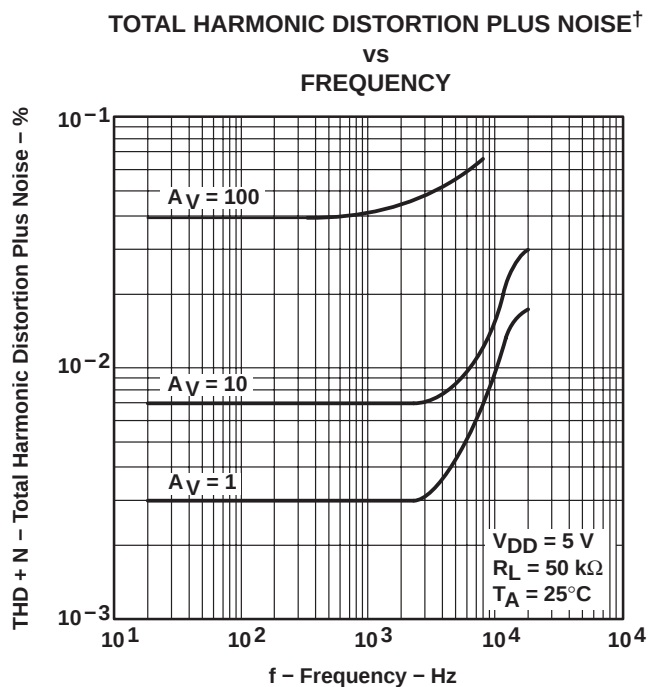


Figure 54

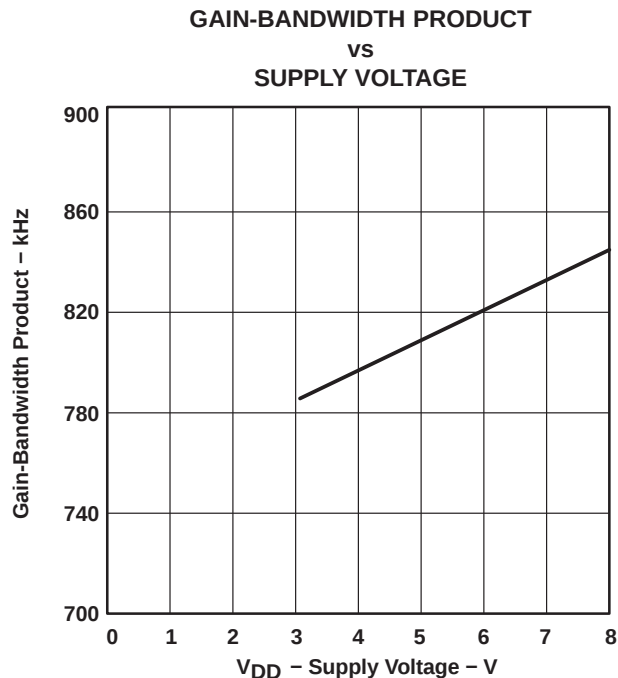


Figure 55

† For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V.

TYPICAL CHARACTERISTICS

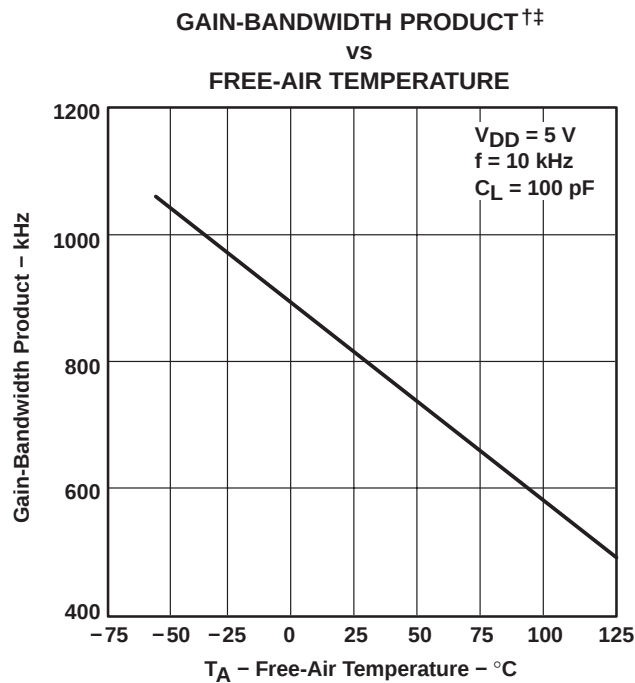


Figure 56

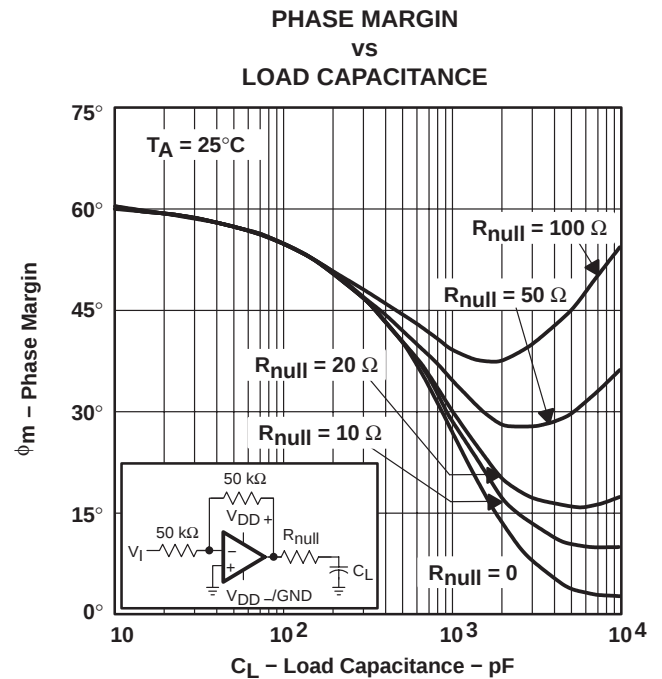


Figure 57

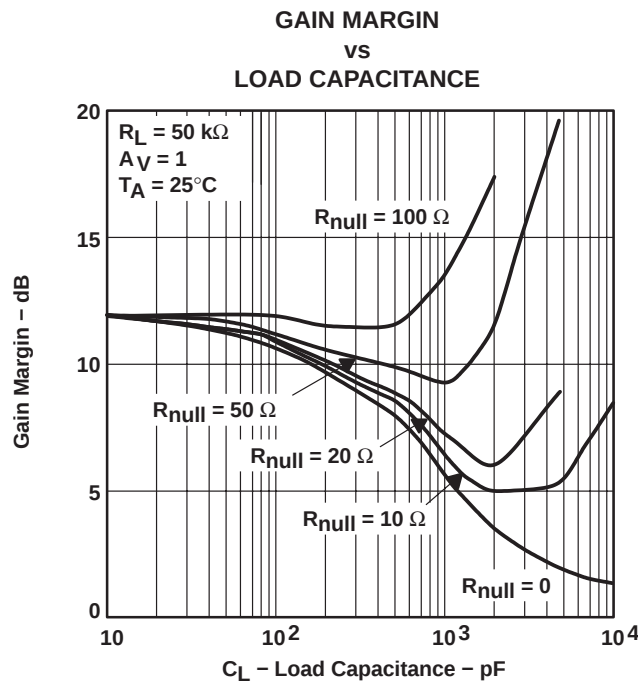


Figure 58

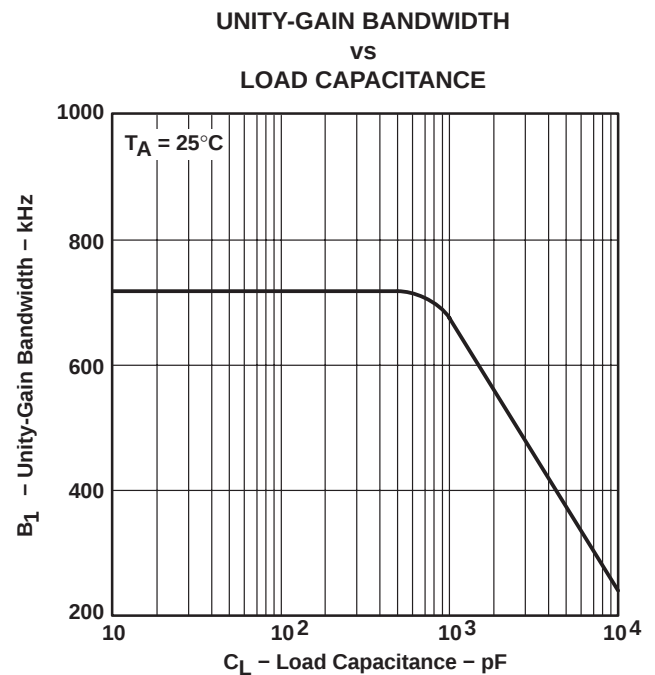


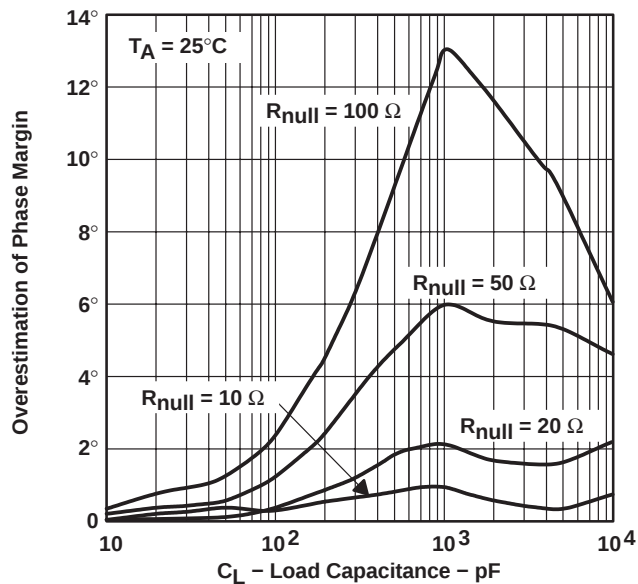
Figure 59

† For all curves where $V_{DD} = 5\text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3\text{ V}$, all loads are referenced to 1.5 V.

‡ Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS

OVERESTIMATION OF PHASE MARGIN† vs LOAD CAPACITANCE



† See application information

Figure 60

APPLICATION INFORMATION

driving large capacitive loads

The TLV226x is designed to drive larger capacitive loads than most CMOS operational amplifiers. Figure 51 and Figure 52 illustrate its ability to drive loads greater than 400 pF while maintaining good gain and phase margins ($R_{null} = 0$).

A smaller series resistor (R_{null}) at the output of the device (see Figure 61) improves the gain and phase margins when driving large capacitive loads. Figure 51 and Figure 52 show the effects of adding series resistances of 10 Ω , 20 Ω , 50 Ω , and 100 Ω . The addition of this series resistor has two effects: the first is that it adds a zero to the transfer function and the second is that it reduces the frequency of the pole associated with the output load in the transfer function.

The zero introduced to the transfer function is equal to the series resistance times the load capacitance. To calculate the improvement in phase margin, equation (1) can be used.

$$\Delta\theta_{m1} = \tan^{-1} \left(2 \times \pi \times \text{UGBW} \times R_{null} \times C_L \right) \quad (1)$$

Where :

$\Delta\theta_{m1}$ = improvement in phase margin

UGBW = unity-gain bandwidth frequency

R_{null} = output series resistance

C_L = load capacitance

The unity-gain bandwidth (UGBW) frequency decreases as the capacitive load increases (see Figure 53). To use equation 1, UGBW must be approximated from Figure 53.

Using equation 1 alone overestimates the improvement in phase margin as illustrated in Figure 59. The overestimation is caused by the decrease in the frequency of the pole associated with the load, providing additional phase shift and reducing the overall improvement in phase margin. The pole associated with the load is reduced by the factor calculated in equation 2.

$$F = \frac{1}{1 + g_m \times R_{null}} \quad (2)$$

Where :

F = factor reducing frequency of pole

g_m = small-signal output transconductance (typically 4.83×10^{-3} mhos)

R_{null} = output series resistance

For the TLV226x, the pole associated with the load is typically 7 MHz with 100-pF load capacitance. This value varies inversely with C_L : at $C_L = 10$ pF, use 70 MHz, at $C_L = 1000$ pF, use 700 kHz, and so on.

Reducing the pole associated with the load introduces phase shift, thereby reducing phase margin. This results in an error in the increase in phase margin expected by considering the zero alone (equation 1). Equation 3 approximates the reduction in phase margin due to the movement of the pole associated with the load. The result of this equation can be subtracted from the result of the equation 1 to better approximate the improvement in phase margin.

APPLICATION INFORMATION

driving large capacitive loads (continued)

$$\Delta\theta_{m2} = \tan^{-1} \left[\frac{UGBW}{(F \times P_2)} \right] - \tan^{-1} \left(\frac{UGBW}{P_2} \right) \quad (3)$$

Where :

$\Delta\theta_{m2}$ = reduction in phase margin

UGBW = unity-gain bandwidth frequency

F = factor from equation (2)

P_2 = unadjusted pole (70 MHz @ 10 pF, 7 MHz @ 100 pF, etc.)

Using these equations with Figure 60 and Figure 61 enables the designer to choose the appropriate output series resistance to optimize the design of circuits driving large capacitive loads.



Figure 61. Series-Resistance Circuit

APPLICATION INFORMATION

macromodel information

Macromodel information provided was derived using Microsim *Parts*™, the model generation software used with Microsim *PSpice*™. The Boyle macromodel (see Note 5) and subcircuit in Figure 62 are generated using the TLV226x typical electrical and operating characteristics at $T_A = 25^\circ\text{C}$. Using this information, output simulations of the following key parameters can be generated to a tolerance of 20% (in most cases):

- Maximum positive output voltage swing
- Maximum negative output voltage swing
- Slew rate
- Quiescent power dissipation
- Input bias current
- Open-loop voltage amplification
- Unity-gain frequency
- Common-mode rejection ratio
- Phase margin
- DC output resistance
- AC output resistance
- Short-circuit output current limit

NOTE 5: G. R. Boyle, B. M. Cohn, D. O. Pederson, and J. E. Solomon, "Macromodeling of Integrated Circuit Operational Amplifiers," *IEEE Journal of Solid-State Circuits*, SC-9, 353 (1974).



Figure 62. Boyle Macromodel and Subcircuit

PSpice and *Parts* are trademarks of MicroSim Corporation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
5962-9550401QPA	Active	Production	CDIP (JG) 8	50 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	9550401QPA TLV2262M
5962-9550403QHA	Active	Production	CFP (U) 10	25 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	9550403QHA TLV2262AM
5962-9550403QPA	Active	Production	CDIP (JG) 8	50 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	9550403QPA TLV2262AM
5962-9550404QCA	Active	Production	CDIP (J) 14	25 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962-9550404QC A TLV2264AMJB
5962-9550404QDA	Active	Production	CFP (W) 14	25 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962-9550404QD A TLV2264AMWB
TLV2262AID	Active	Production	SOIC (D) 8	75 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	V2262A
TLV2262AID.A	Active	Production	SOIC (D) 8	75 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	V2262A
TLV2262AIDR	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	V2262A
TLV2262AIDR.A	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	V2262A
TLV2262AIP	Active	Production	PDIP (P) 8	50 TUBE	Yes	NIPDAU	N/A for Pkg Type	-40 to 125	TLV2262AI
TLV2262AIP.A	Active	Production	PDIP (P) 8	50 TUBE	Yes	NIPDAU	N/A for Pkg Type	-40 to 125	TLV2262AI
TLV2262AIPW	Obsolete	Production	TSSOP (PW) 8	-	-	Call TI	Call TI	-40 to 125	TY262A
TLV2262AIPWR	Active	Production	TSSOP (PW) 8	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TY262A
TLV2262AIPWR.A	Active	Production	TSSOP (PW) 8	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TY262A
TLV2262AMJGB	Active	Production	CDIP (JG) 8	50 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	9550403QPA TLV2262AM
TLV2262AMJGB.A	Active	Production	CDIP (JG) 8	50 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	9550403QPA TLV2262AM
TLV2262AMUB	Active	Production	CFP (U) 10	25 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	9550403QHA TLV2262AM
TLV2262AMUB.A	Active	Production	CFP (U) 10	25 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	9550403QHA TLV2262AM
TLV2262ID	Active	Production	SOIC (D) 8	75 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	V2262I
TLV2262ID.A	Active	Production	SOIC (D) 8	75 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	V2262I
TLV2262IDR	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	V2262I

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TLV2262IDR.A	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	V2262I
TLV2262IDRG4	Active	Production	SOIC (D) 8	2500 LARGE T&R	-	Call TI	Call TI	-40 to 125	
TLV2262IP	Active	Production	PDIP (P) 8	50 TUBE	Yes	NIPDAU	N/A for Pkg Type	-40 to 125	TLV2262IP
TLV2262IP.A	Active	Production	PDIP (P) 8	50 TUBE	Yes	NIPDAU	N/A for Pkg Type	-40 to 125	TLV2262IP
TLV2262IPW	Obsolete	Production	TSSOP (PW) 8	-	-	Call TI	Call TI	-40 to 125	TY2262
TLV2262IPWR	Active	Production	TSSOP (PW) 8	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TY2262
TLV2262IPWR.A	Active	Production	TSSOP (PW) 8	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TY2262
TLV2262MJGB	Active	Production	CDIP (JG) 8	50 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	9550401QPA TLV2262M
TLV2262MJGB.A	Active	Production	CDIP (JG) 8	50 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	9550401QPA TLV2262M
TLV2264AID	Active	Production	SOIC (D) 14	50 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	V2264AI
TLV2264AID.B	Active	Production	SOIC (D) 14	50 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	V2264AI
TLV2264AIDR	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	V2264AI
TLV2264AIDR.B	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	V2264AI
TLV2264AIDRG4	Active	Production	SOIC (D) 14	2500 LARGE T&R	-	Call TI	Call TI	-40 to 125	
TLV2264AIN	Active	Production	PDIP (N) 14	25 TUBE	Yes	NIPDAU	N/A for Pkg Type	-40 to 125	TLV2264AIN
TLV2264AIN.A	Active	Production	PDIP (N) 14	25 TUBE	Yes	NIPDAU	N/A for Pkg Type	-40 to 125	TLV2264AIN
TLV2264AIPWR	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	P2264AI
TLV2264AIPWR.B	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	P2264AI
TLV2264AMJB	Active	Production	CDIP (J) 14	25 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962-9550404QC A TLV2264AMJB
TLV2264AMJB.A	Active	Production	CDIP (J) 14	25 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962-9550404QC A TLV2264AMJB
TLV2264AMWB	Active	Production	CFP (W) 14	25 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962-9550404QD A TLV2264AMWB
TLV2264AMWB.A	Active	Production	CFP (W) 14	25 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962-9550404QD A TLV2264AMWB
TLV2264AQD	Active	Production	SOIC (D) 14	50 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TLV2264A

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TLV2264AQD.A	Active	Production	SOIC (D) 14	50 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TLV2264A
TLV2264AQD.B	Active	Production	SOIC (D) 14	50 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TLV2264A
TLV2264ID	Active	Production	SOIC (D) 14	50 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TLV2264I
TLV2264ID.B	Active	Production	SOIC (D) 14	50 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TLV2264I
TLV2264IDR	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TLV2264I
TLV2264IDR.B	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TLV2264I
TLV2264IN	Active	Production	PDIP (N) 14	25 TUBE	Yes	NIPDAU	N/A for Pkg Type	-40 to 125	TLV2264IN
TLV2264IN.A	Active	Production	PDIP (N) 14	25 TUBE	Yes	NIPDAU	N/A for Pkg Type	-40 to 125	TLV2264IN
TLV2264IPWR	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	P2264I
TLV2264IPWR.B	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	P2264I
TLV2264QD	Active	Production	SOIC (D) 14	50 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TLV2264
TLV2264QD.A	Active	Production	SOIC (D) 14	50 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TLV2264
TLV2264QD.B	Active	Production	SOIC (D) 14	50 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TLV2264

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "-" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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OTHER QUALIFIED VERSIONS OF TLV2262, TLV2262A, TLV2262AM, TLV2262M, TLV2264A, TLV2264AM :

- Catalog : [TLV2262A](#), [TLV2262](#), [TLV2264A](#)
- Automotive : [TLV2262A-Q1](#), [TLV2262A-Q1](#), [TLV2264A-Q1](#), [TLV2264A-Q1](#)
- Military : [TLV2262M](#), [TLV2262AM](#), [TLV2264AM](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product
- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects
- Military - QML certified for Military and Defense Applications

TAPE AND REEL INFORMATION



*All dimensions are nominal

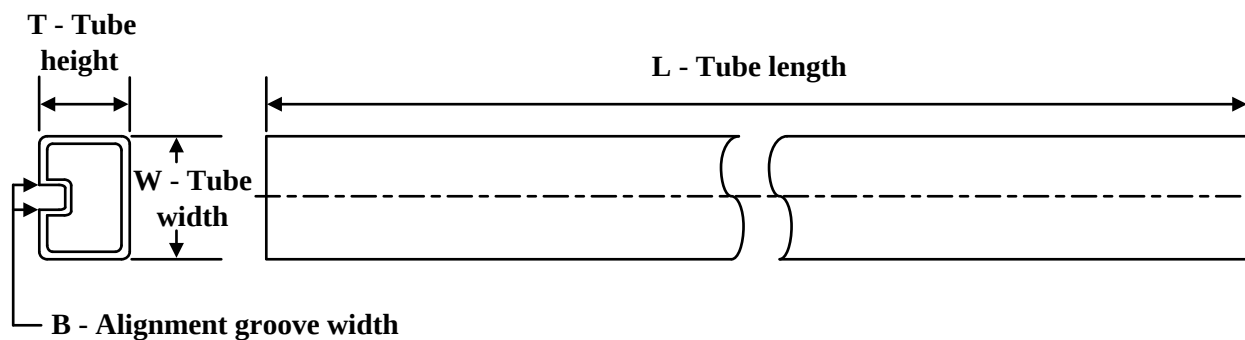
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV2262AIDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLV2262AIPWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
TLV2262IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLV2262IPWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
TLV2264AIDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLV2264AIPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TLV2264IDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLV2264IPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV2262AIDR	SOIC	D	8	2500	353.0	353.0	32.0
TLV2262AIPWR	TSSOP	PW	8	2000	353.0	353.0	32.0
TLV2262IDR	SOIC	D	8	2500	353.0	353.0	32.0
TLV2262IPWR	TSSOP	PW	8	2000	353.0	353.0	32.0
TLV2264AIDR	SOIC	D	14	2500	340.5	336.1	32.0
TLV2264AIPWR	TSSOP	PW	14	2000	353.0	353.0	32.0
TLV2264IDR	SOIC	D	14	2500	353.0	353.0	32.0
TLV2264IPWR	TSSOP	PW	14	2000	353.0	353.0	32.0

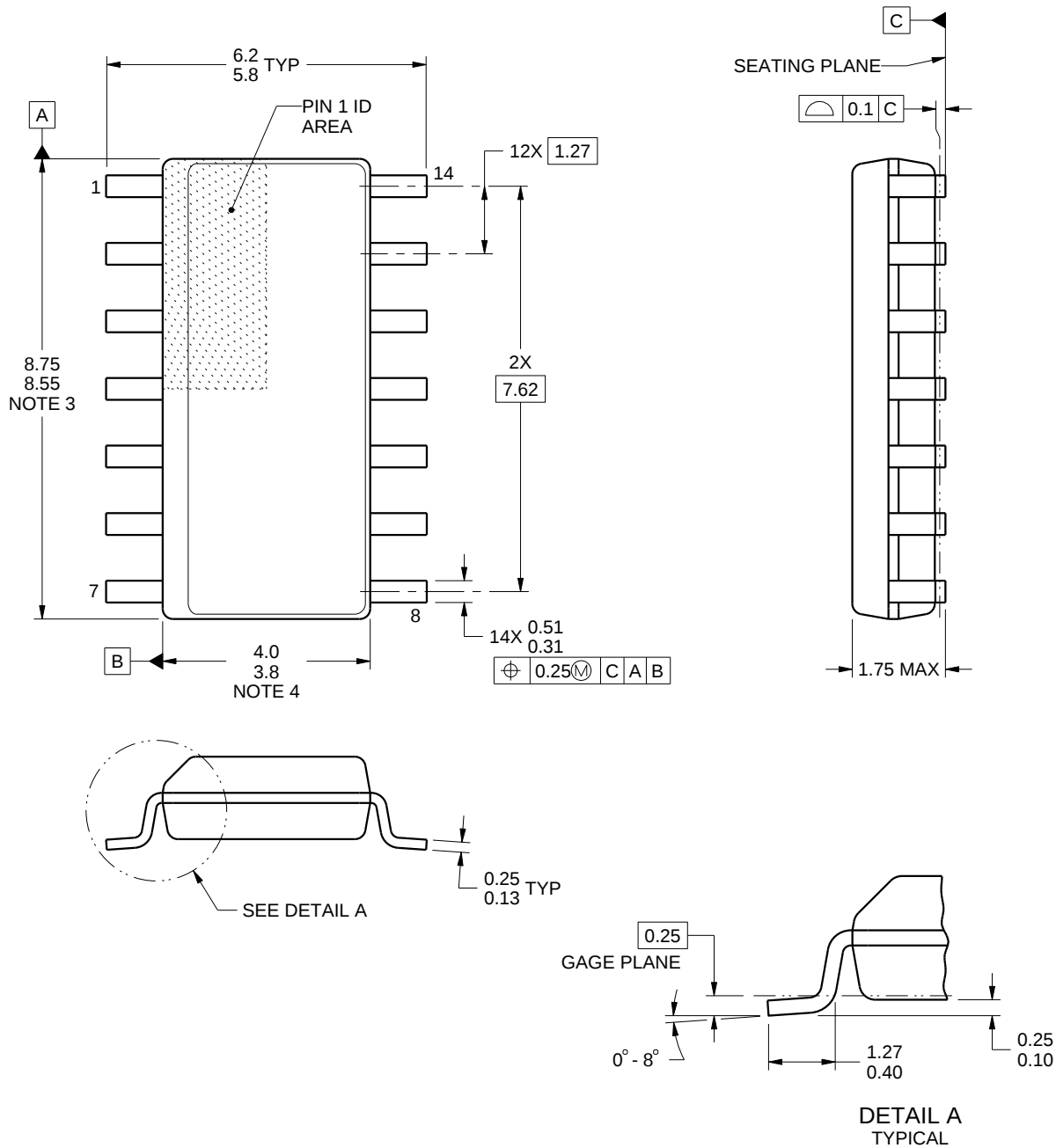
TUBE


*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
5962-9550403QHA	U	CFP	10	25	506.98	26.16	6220	NA
5962-9550404QDA	W	CFP	14	25	506.98	26.16	6220	NA
TLV2262AID	D	SOIC	8	75	507	8	3940	4.32
TLV2262AID.A	D	SOIC	8	75	507	8	3940	4.32
TLV2262AIP	P	PDIP	8	50	506	13.97	11230	4.32
TLV2262AIP.A	P	PDIP	8	50	506	13.97	11230	4.32
TLV2262AMUB	U	CFP	10	25	506.98	26.16	6220	NA
TLV2262AMUB.A	U	CFP	10	25	506.98	26.16	6220	NA
TLV2262ID	D	SOIC	8	75	507	8	3940	4.32
TLV2262ID.A	D	SOIC	8	75	507	8	3940	4.32
TLV2262IP	P	PDIP	8	50	506	13.97	11230	4.32
TLV2262IP.A	P	PDIP	8	50	506	13.97	11230	4.32
TLV2264AID	D	SOIC	14	50	507	8	3940	4.32
TLV2264AID.B	D	SOIC	14	50	507	8	3940	4.32
TLV2264AIN	N	PDIP	14	25	506	13.97	11230	4.32
TLV2264AIN.A	N	PDIP	14	25	506	13.97	11230	4.32
TLV2264AMWB	W	CFP	14	25	506.98	26.16	6220	NA
TLV2264AMWB.A	W	CFP	14	25	506.98	26.16	6220	NA
TLV2264AQD	D	SOIC	14	50	507	8	3940	4.32
TLV2264AQD.A	D	SOIC	14	50	507	8	3940	4.32
TLV2264AQD.B	D	SOIC	14	50	507	8	3940	4.32
TLV2264ID	D	SOIC	14	50	507	8	3940	4.32
TLV2264ID.B	D	SOIC	14	50	507	8	3940	4.32
TLV2264IN	N	PDIP	14	25	506	13.97	11230	4.32
TLV2264IN.A	N	PDIP	14	25	506	13.97	11230	4.32
TLV2264QD	D	SOIC	14	50	505.46	6.76	3810	4
TLV2264QD.A	D	SOIC	14	50	505.46	6.76	3810	4
TLV2264QD.B	D	SOIC	14	50	505.46	6.76	3810	4

D0014A**PACKAGE OUTLINE****SOIC - 1.75 mm max height**

SMALL OUTLINE INTEGRATED CIRCUIT



4220718/A 09/2016

NOTES:

1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm, per side.
5. Reference JEDEC registration MS-012, variation AB.

EXAMPLE BOARD LAYOUT

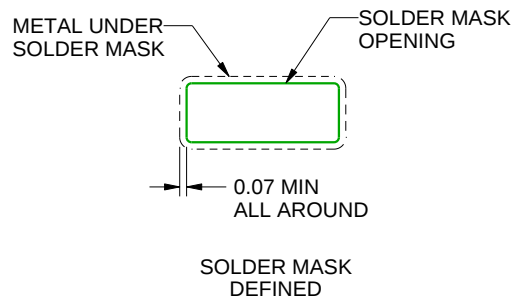
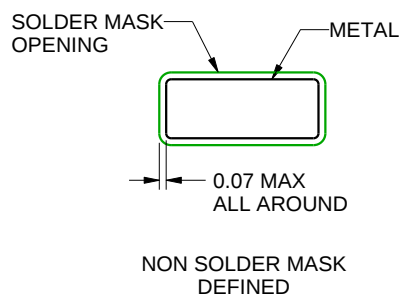
D0014A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE
SCALE:8X



SOLDER MASK DETAILS

4220718/A 09/2016

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

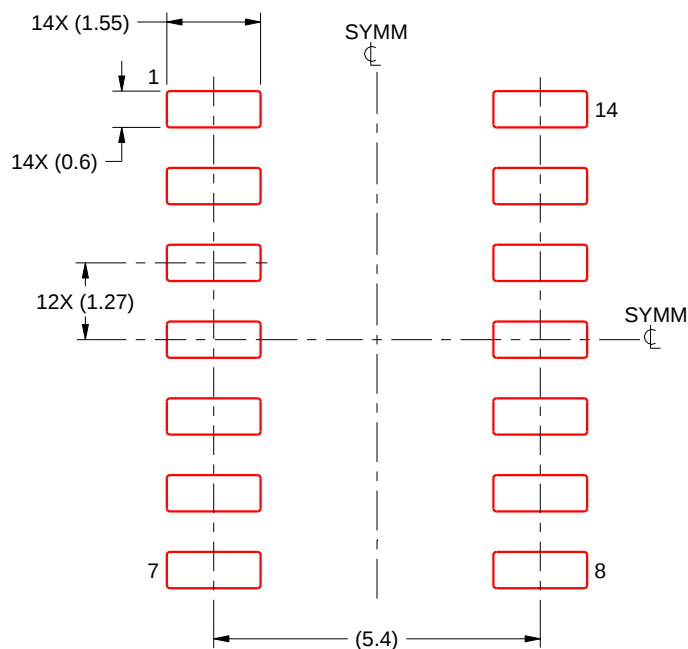
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0014A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:8X

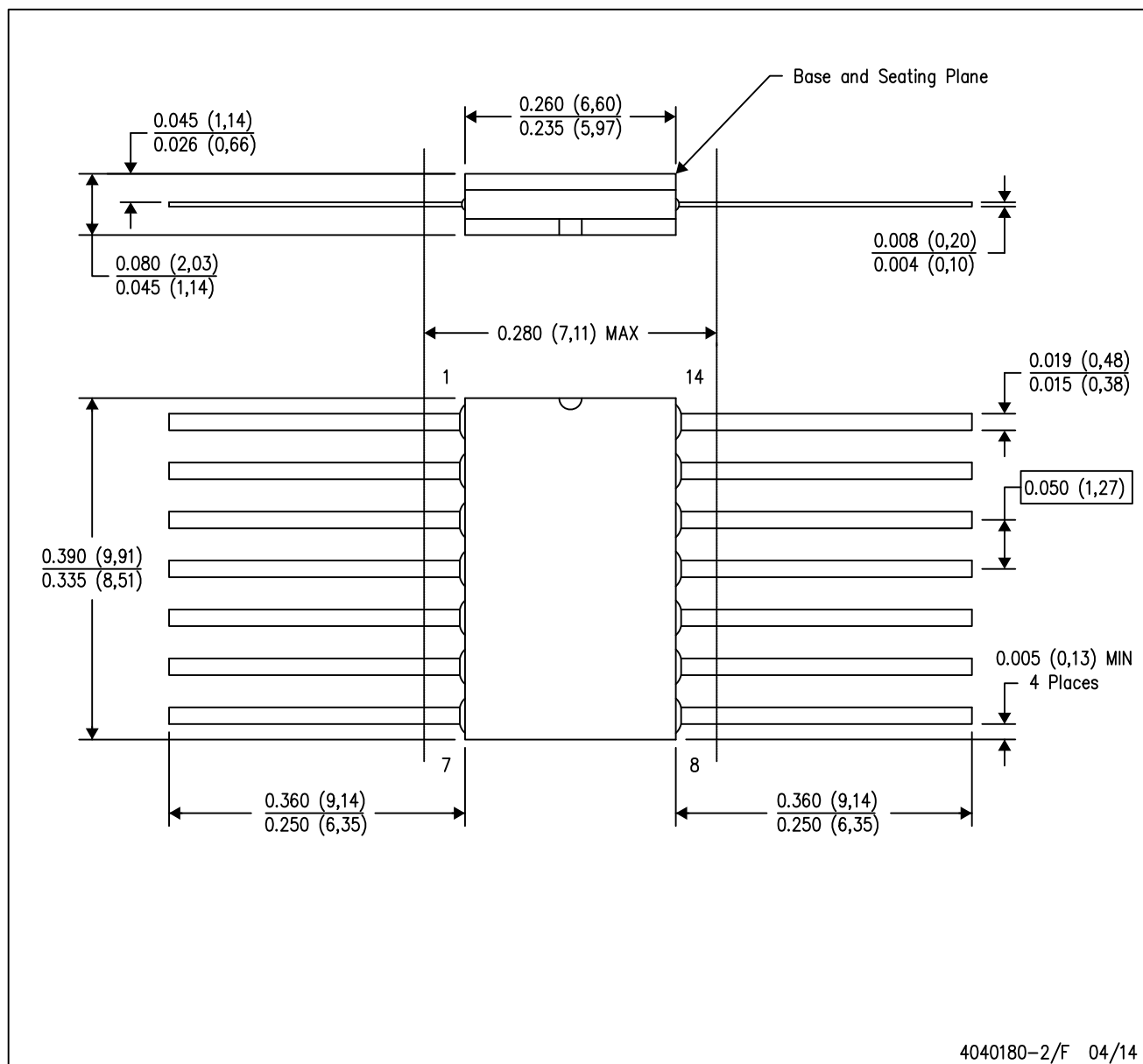
4220718/A 09/2016

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

W (R-GDFP-F14)

CERAMIC DUAL FLATPACK



NOTES:

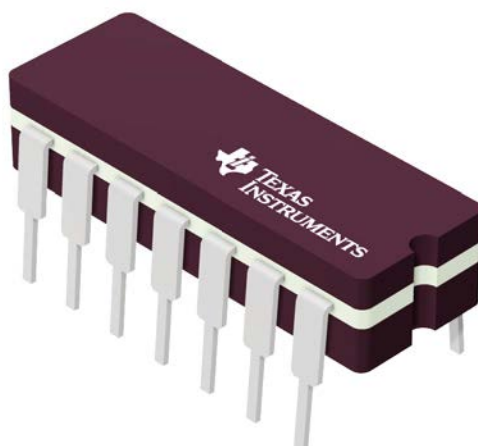
- All linear dimensions are in inches (millimeters).
- This drawing is subject to change without notice.
- This package can be hermetically sealed with a ceramic lid using glass frit.
- Index point is provided on cap for terminal identification only.
- Falls within MIL STD 1835 GDFP1-F14

J 14

GENERIC PACKAGE VIEW

CDIP - 5.08 mm max height

CERAMIC DUAL IN LINE PACKAGE



Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

4040083-5/G

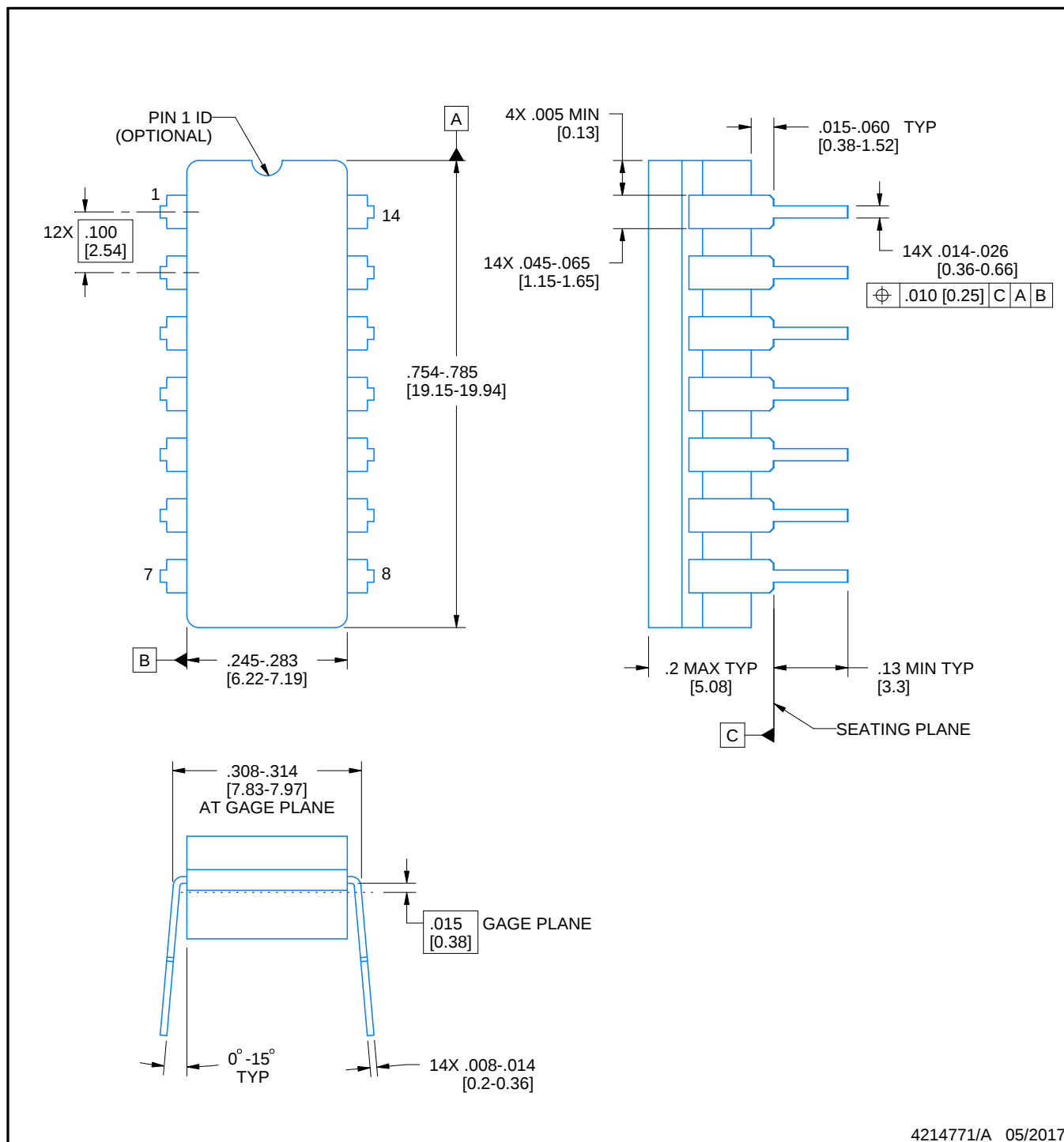


J0014A

PACKAGE OUTLINE

CDIP - 5.08 mm max height

CERAMIC DUAL IN LINE PACKAGE



4214771/A 05/2017

NOTES:

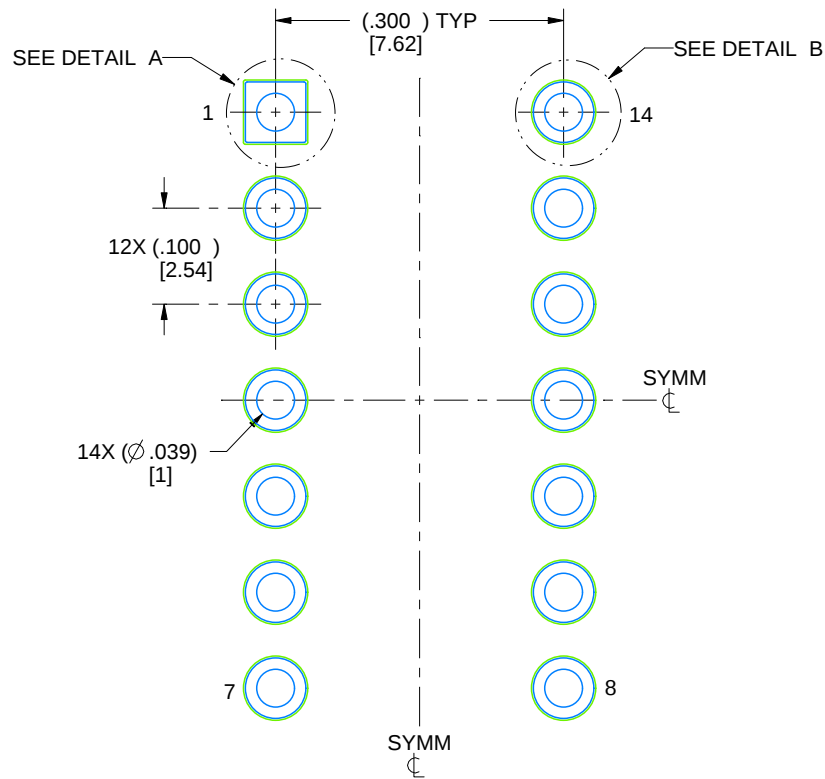
1. All controlling linear dimensions are in inches. Dimensions in brackets are in millimeters. Any dimension in brackets or parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This package is hermetically sealed with a ceramic lid using glass frit.
4. Index point is provided on cap for terminal identification only and on press ceramic glass frit seal only.
5. Falls within MIL-STD-1835 and GDIP1-T14.

EXAMPLE BOARD LAYOUT

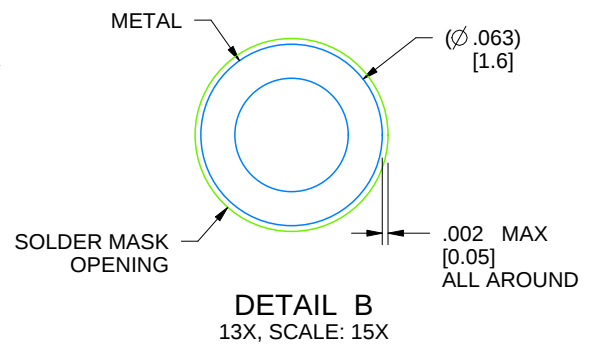
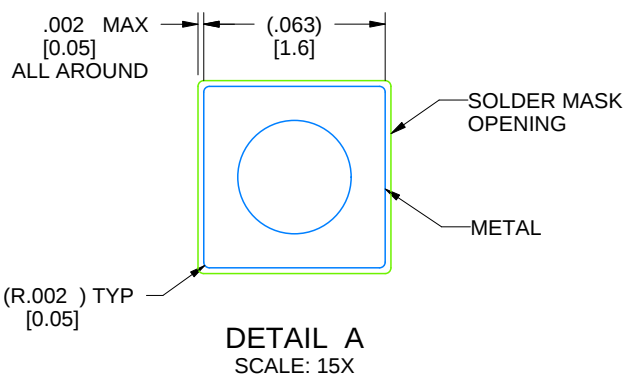
J0014A

CDIP - 5.08 mm max height

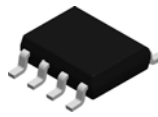
CERAMIC DUAL IN LINE PACKAGE



LAND PATTERN EXAMPLE
NON-SOLDER MASK DEFINED
SCALE: 5X



4214771/A 05/2017

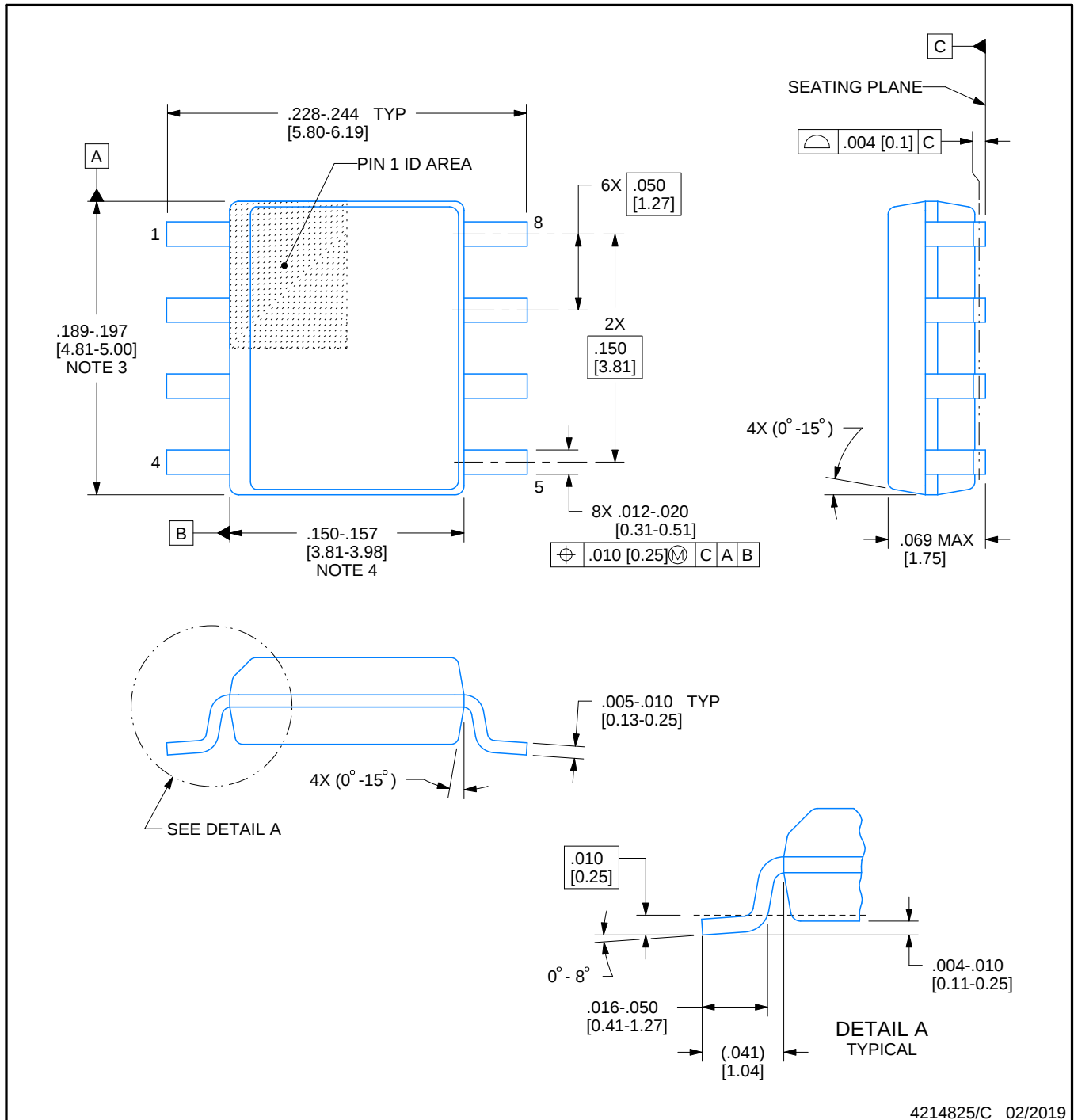


D0008A

PACKAGE OUTLINE

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



4214825/C 02/2019

NOTES:

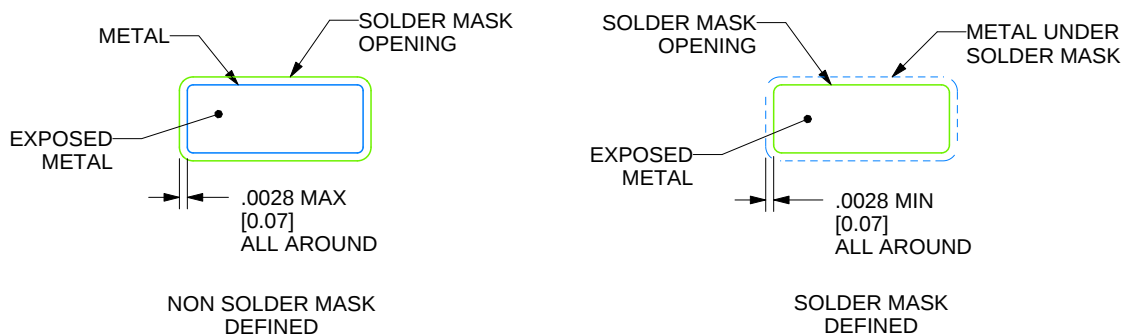
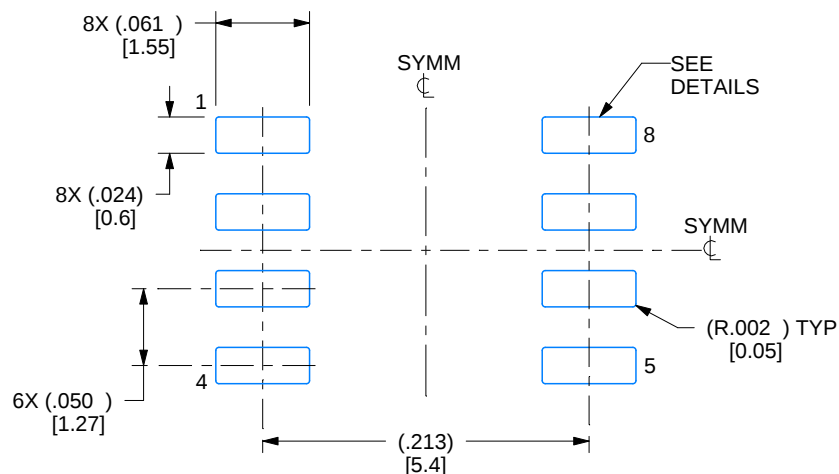
1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MS-012, variation AA.

EXAMPLE BOARD LAYOUT

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



4214825/C 02/2019

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

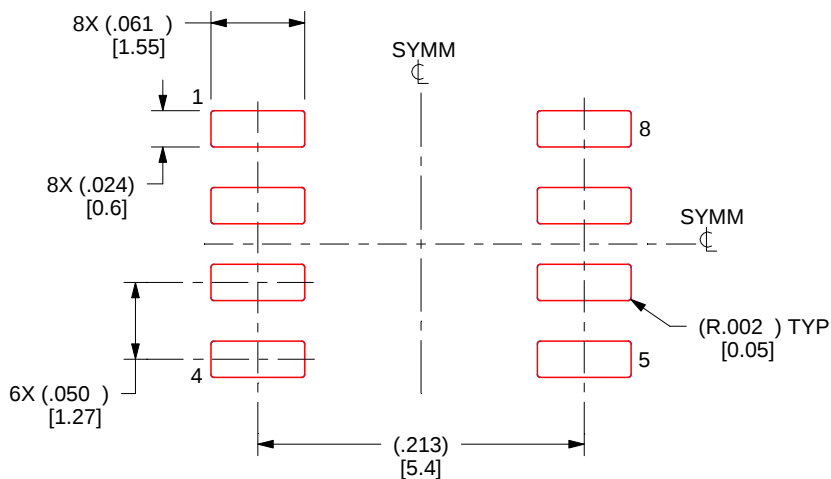
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.125 MM] THICK STENCIL
SCALE:8X

4214825/C 02/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

P (R-PDIP-T8)

PLASTIC DUAL-IN-LINE PACKAGE

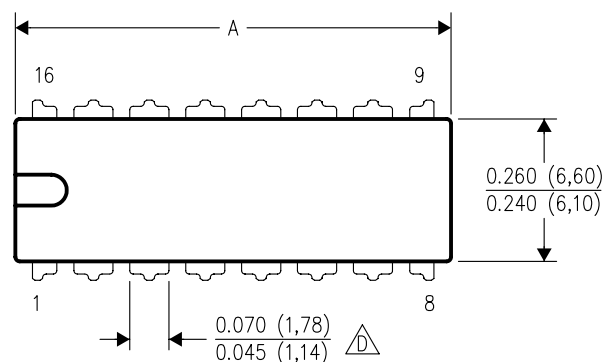


- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - C. Falls within JEDEC MS-001 variation BA.

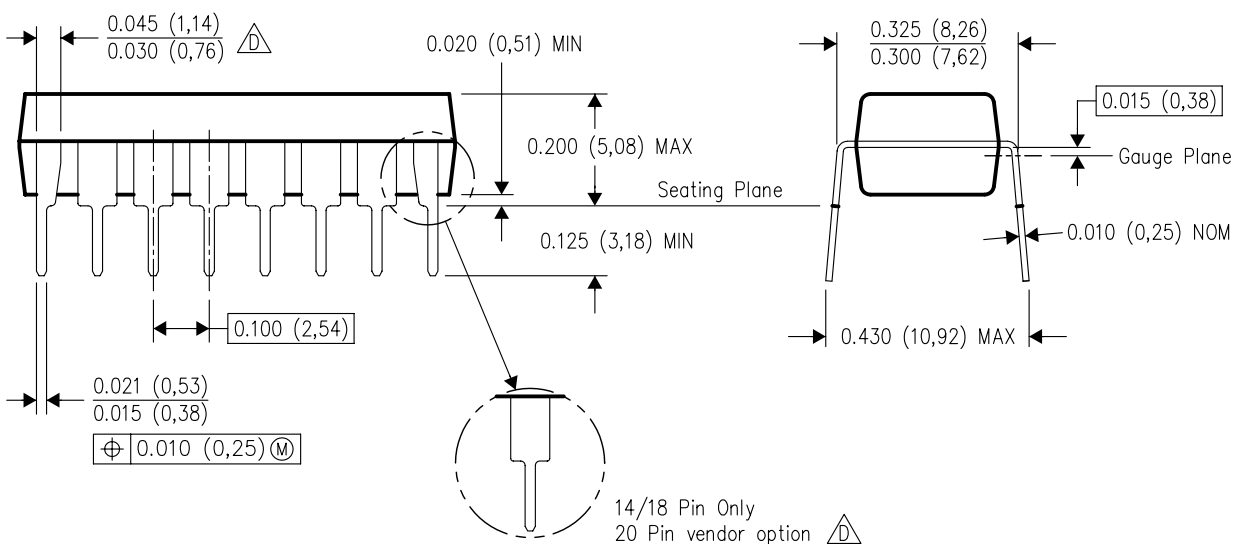
N (R-PDIP-T**)

16 PINS SHOWN

PLASTIC DUAL-IN-LINE PACKAGE



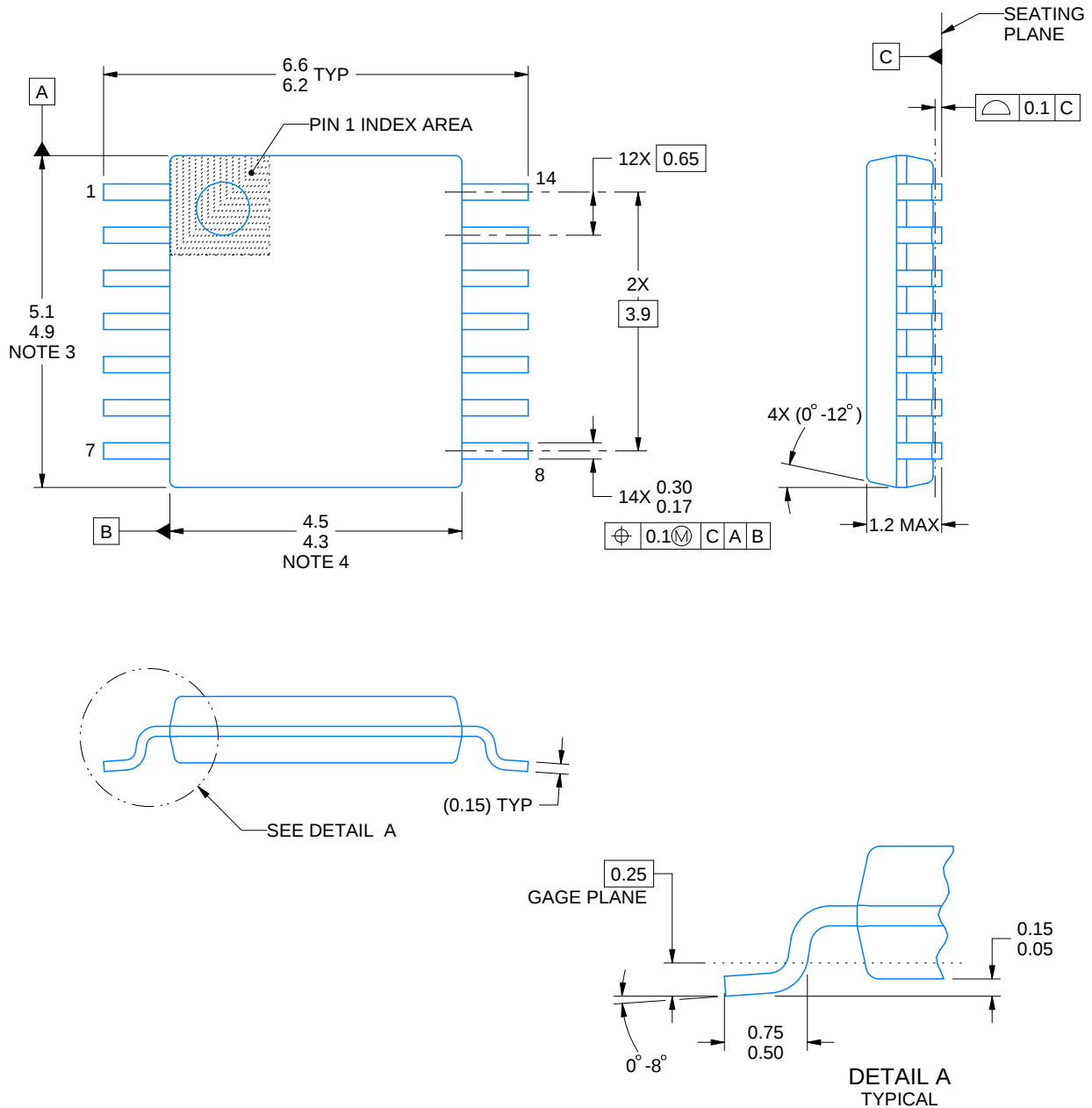
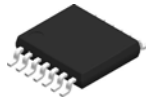
PINS ** DIM	14	16	18	20
A MAX	0.775 (19,69)	0.775 (19,69)	0.920 (23,37)	1.060 (26,92)
A MIN	0.745 (18,92)	0.745 (18,92)	0.850 (21,59)	0.940 (23,88)
MS-001 VARIATION	AA	BB	AC	AD



4040049/E 12/2002

NOTES:

- A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
-  Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
 The 20 pin end lead shoulder width is a vendor option, either half or full width.



4220202/B 12/2023

NOTES:

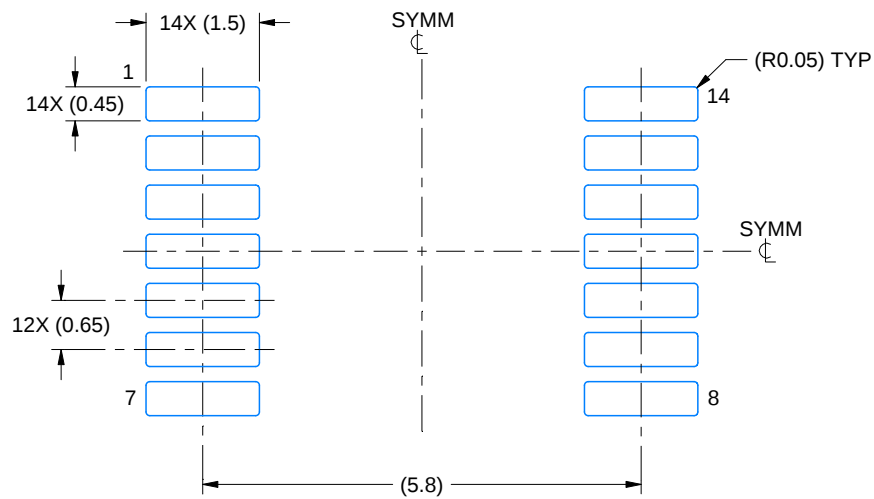
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.

EXAMPLE BOARD LAYOUT

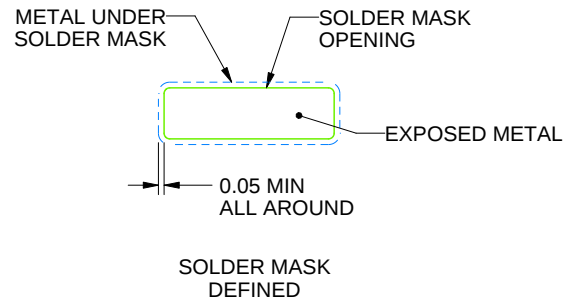
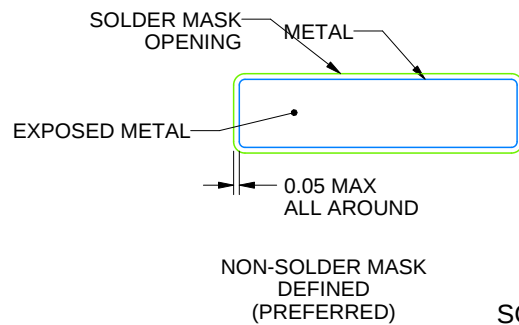
PW0014A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X



SOLDER MASK DETAILS

4220202/B 12/2023

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

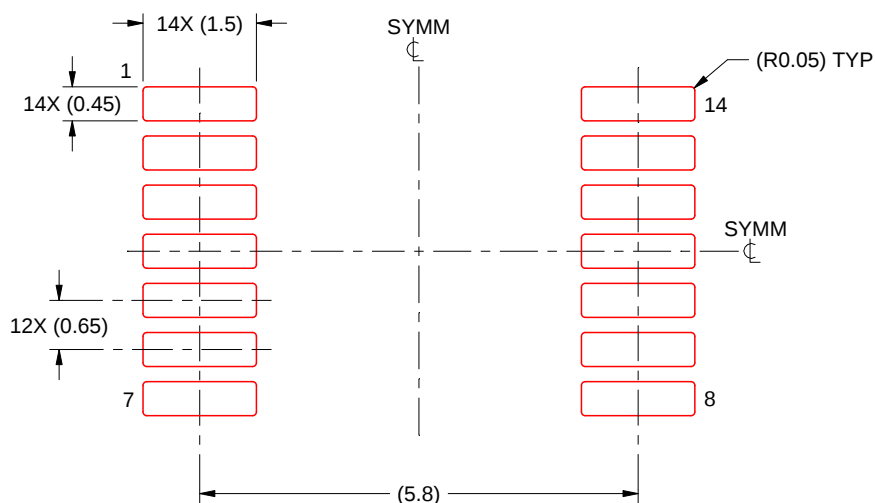
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

PW0014A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220202/B 12/2023

NOTES: (continued)

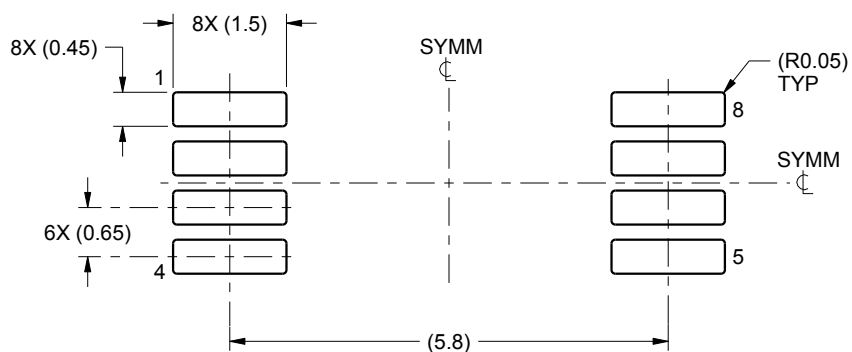
8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

EXAMPLE BOARD LAYOUT

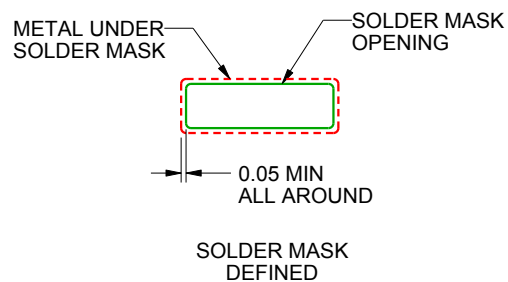
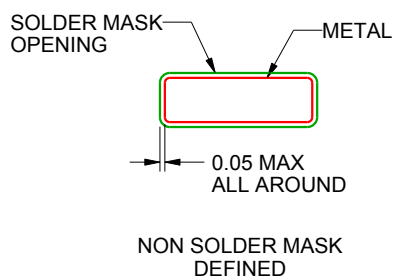
PW0008A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
SCALE:10X



SOLDER MASK DETAILS
NOT TO SCALE

4221848/A 02/2015

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

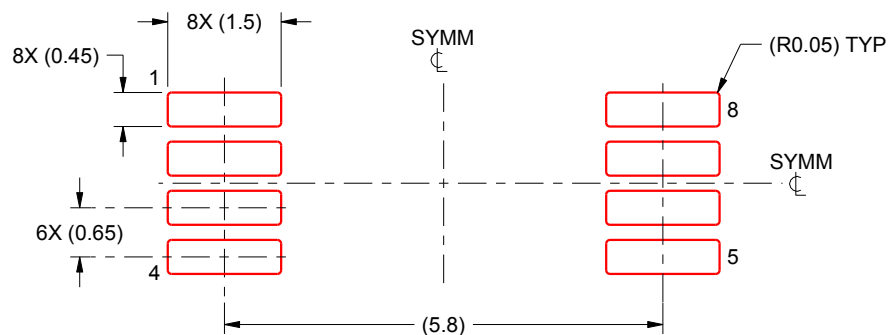
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

PW0008A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:10X

4221848/A 02/2015

NOTES: (continued)

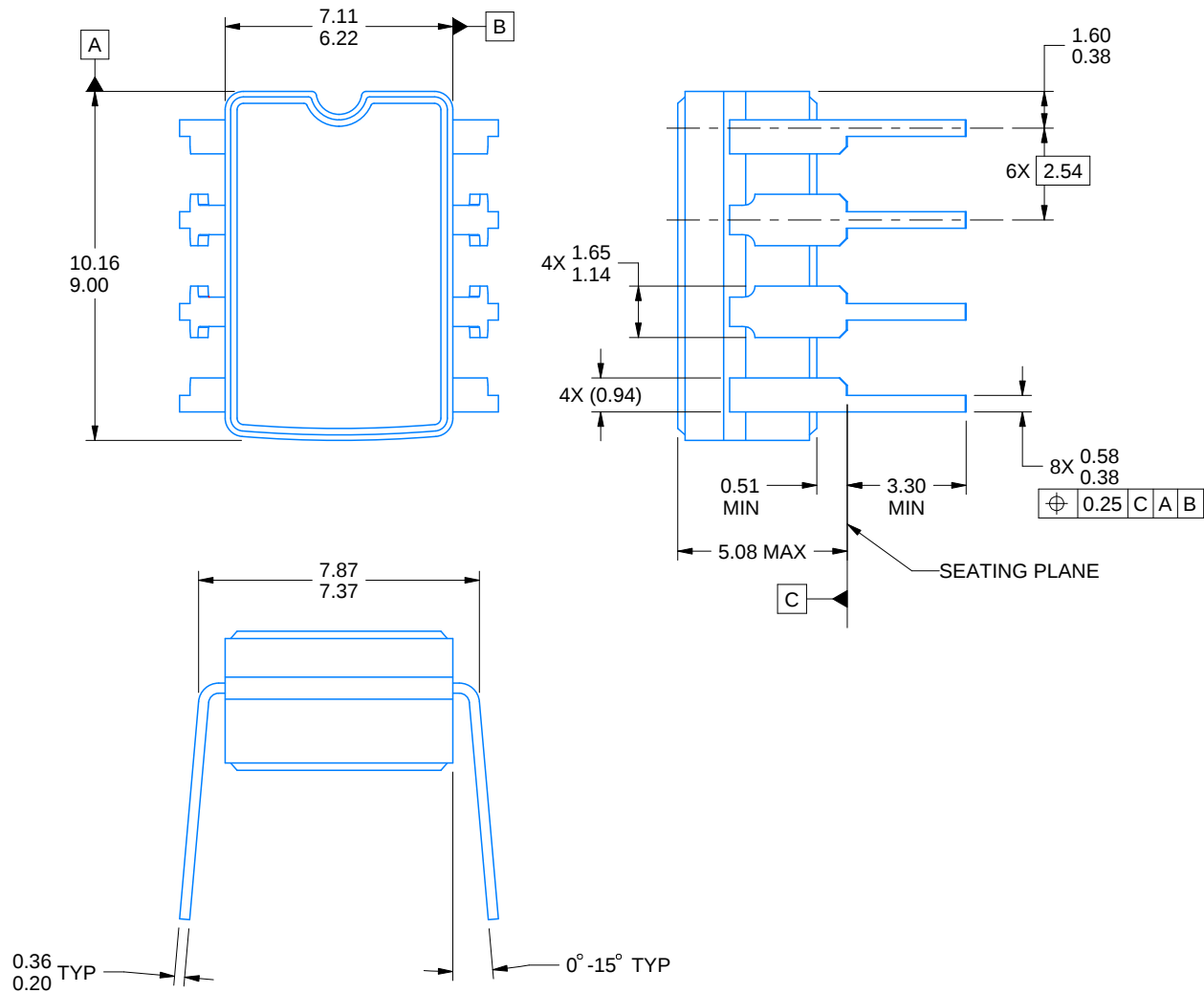
8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

JG0008A

PACKAGE OUTLINE

CDIP - 5.08 mm max height

CERAMIC DUAL IN-LINE PACKAGE



4230036/A 09/2023

NOTES:

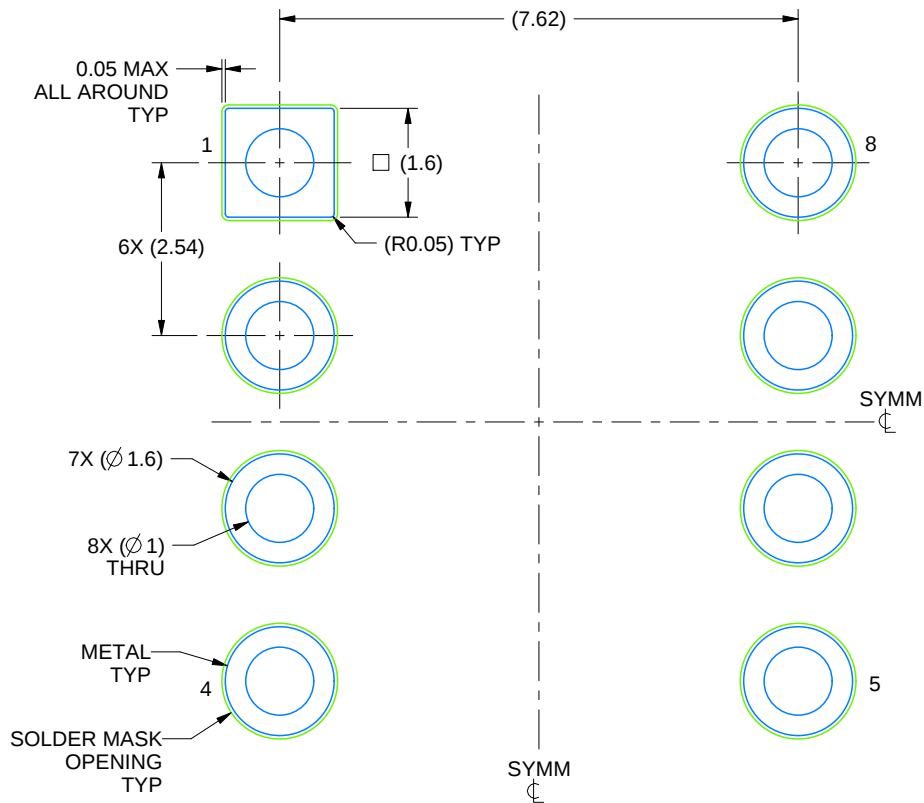
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This package can be hermetically sealed with a ceramic lid using glass frit.
4. Index point is provided on cap for terminal identification.
5. Falls within MIL STD 1835 GDIP1-T8

EXAMPLE BOARD LAYOUT

JG0008A

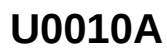
CDIP - 5.08 mm max height

CERAMIC DUAL IN-LINE PACKAGE



LAND PATTERN EXAMPLE
NON SOLDER MASK DEFINED
SCALE: 9X

4230036/A 09/2023



CFP - 2.03 mm max height

CERAMIC FLATPACK



1. All linear dimensions are in inches. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

2. This drawing is subject to change without notice.

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